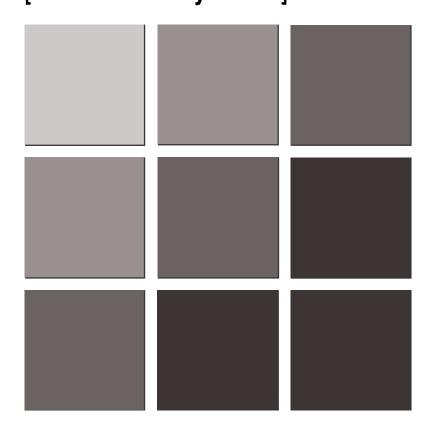
FUJITSU MICROELECTRONICS PRODUCT GUIDE

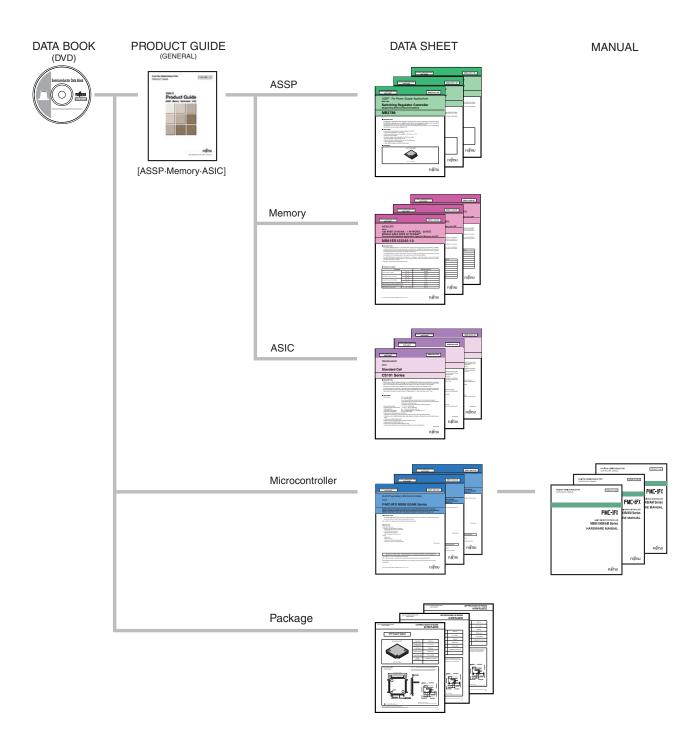
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2009.10 **Product Guide** [ASSP•Memory•ASIC]





Technical Documentation of Electronic Devices



Telephone Products Mobile, Wireless Communication Products Communication Network Display Control Products 1. Video/Audio Products Digital Demodulator 2. ISDB-T OFDM. 2. Video Encoder, Decoder Power Management Applications Motor Drivers 3. RFID (FerVID family) 3. General-Purpose Converter 3. SD/SDHC card 3. Spread Spectrum Clock Generator Memory Memory Mobile FCRAM (Fast Cycle RAM) Consumer FCRAM (Fast Cycle RAM) FRAM FRAM FRAM 5. Flash Memory Products Scheduled to be out of Production 6. ASIC Standard Cell Macro-Embedded Type Cell Arrays Package Line-up Index Index	ASSP	
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*: SPANSION TM Products

Trademarks

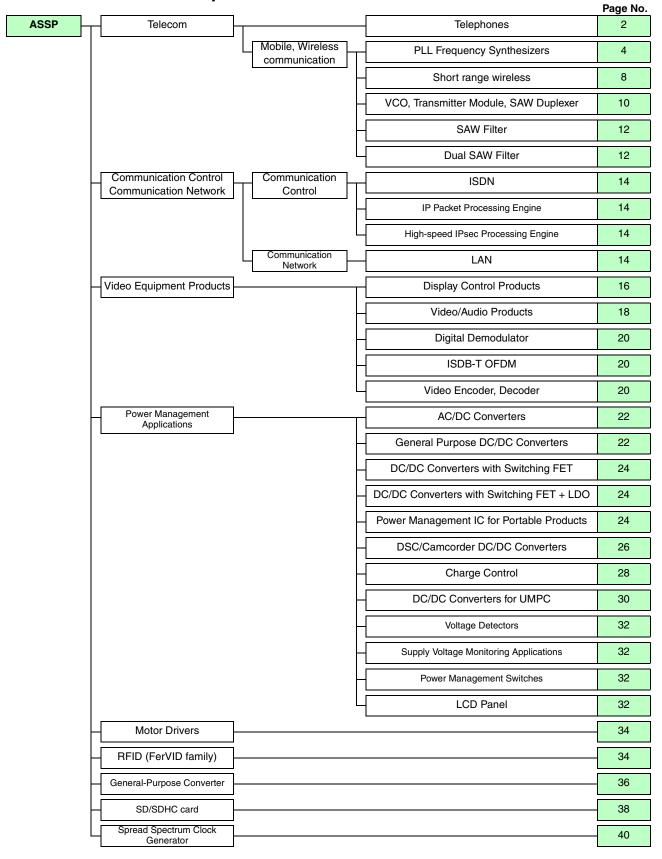
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- Ethernet is a registered trademark of XEROX Corporation in the United States.
- FCRAM is a trademark of Fujitsu Microelectronics Limited, Japan.
- FerVID family is a trademark of Fujitsu Microelectronics Limited, Japan.
- MirrorBit is a trademark of Spansion Inc.
- SPANSION is a trademark of Spansion Inc.
- Amplify is a registered trademark of Synplicity, Inc.

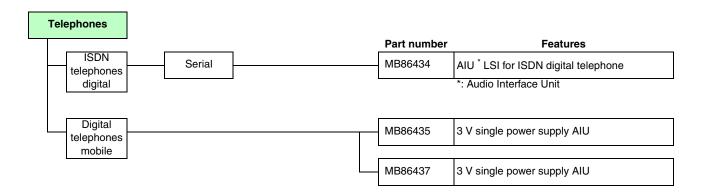
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ASSP Product Line-up

ASSP Product Line-up



Telephone Products



Telephone Products

■ Telephone Products

ISDN Digital Telephone LSIs

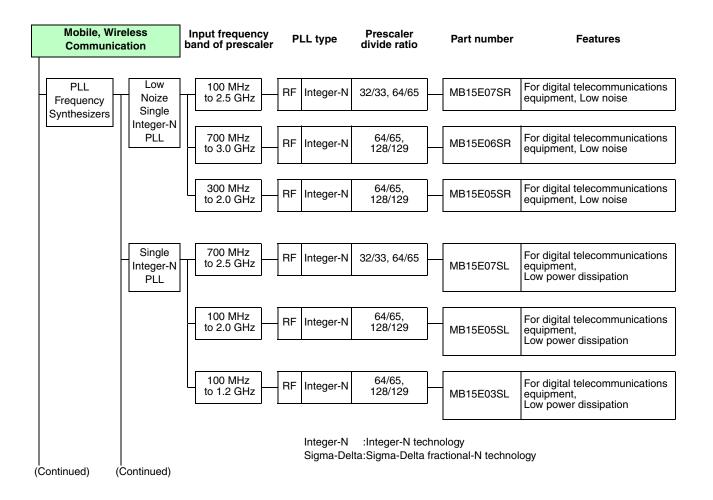
Part number	Functions	CODEC	Power supply voltage (V)	Package QFP
MB86434	AlU for ISDN digital telephones CODEC, DTMF tones, service tone Internal ringer tone	A-laW μ-laW 14-bit linear	+5±5%	64P

Package: P - Plastic

LSIs for Digital Mobile Telephones

Part number	Functions	Compression law	Power supply voltage (V)	Package LQFP
MB86435	A-laW		2.7 to 2.6	64P
MB86437	3 V single power supply AIU	μ-laW linear	2.7 to 3.6	48P

Package: P - Plastic



■ Mobile, Wireless Communication Products

PLL Frequency Synthesizers • Low Noize Single Integer-N PLL

Part number	Inp frequ band		PLL Type		Divide ratio			Power supply current	oly save		save voltage (V)		Package	
	min	max		Prescaler	Program counter	Swallow counter	Reference counter	(mA)	typ (μ A)	min	typ	max	всс	TSSOP
MB15E07SR	100M	2.5G		32/33, 64/65	*	Binary Binary	Binary	8.0	0.1	2.7	3.75	5.0	16P	16P
MB15E06SR	700M	3.0G	Integer -N	64/65, 128/129	11bit 3 to 2047	7bit	14bit	8.0	0.1	2.7	3.0	4.0	16P	16P
MB15E05SR	300M	2.0G		64/65, 128/129	0 10 2047	0 10 127	0 10 10000	7.0	0.1	2.7	3.75	5.0	16P	16P

Package: P - Plastic

• Single Integer-N PLL

Part number	frequ	out ency (Hz)	PLL Type	Divide ra		le ratio	ratio		Power save current		er su oltag (V)	ipply je	Package	
	min	max	1,000	Prescal er	Program counter	Swallow counter	Reference counter	typ (mA)	typ (μ A)	min	typ	max	SSOP	всс
MB15E07SL	700M	2.5G		32/33, 64/65	Dinom		Dinon	4.5	0.1	2.4	3.0	3.6	16P	16P
MB15E05SL	100M	2.0G	Integer -N	64/65, 128/129	11hit I	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	3.5	0.1	2.4	3.0	3.6	16P	16P
MB15E03SL	TOOW	1.2G		64/65, 128/129				2.5	0.1	2.4	3.0	3.6	16P	16P

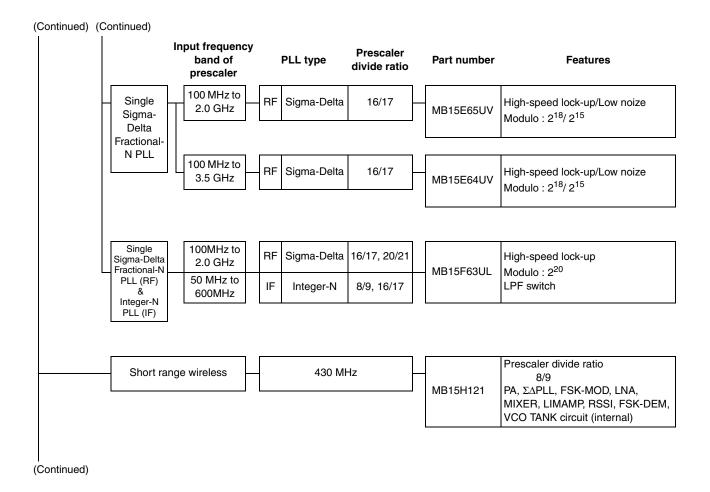
Package: P - Plastic

	Input frequency band of prescaler	PLL type	Prescaler divide ratio		Part number	Features
Dual	400 MHz to 2.6 GHz	RF Integer-N	32/33, 64/65		MB15F78UL	For digital telecommunications equipment
Integer-N PLL	100 MHz to 1.2 GHz	IF Integer-N	16/17, 32/33			Low noise Low power dissipation
	2.0 GHz to 6.0 GHz	RF Integer-N	16/17, 32/33]	MB15F76UL	For digital high-speed telecom-
	100 MHz to 1.5 GHz	IF Integer-N	4/5, 8/9		WID 13F76UL	munications equipment
		(Fixe	ed part 4 division)			
	2.0 GHz to 4.0 GHz	RF Integer-N	64/65, 128/129		MB15F74UV	Small Package For digital high-speed telecommuni-
	200 MHz to 2.0 GHz	IF Integer-N	32/33, 64/65		WD131 740 V	cations equipment
				L	MB15F74UL	For digital high-speed telecom- munications equipment
	200 MHz to 2.25 GHz	RF Integer-N	64/65, 128/129]	MD15F70LIV	Small Package
	50 MHz to 600 MHz	IF Integer-N	8/9, 16/17		MB15F73UV	For digital high-speed telecommunications equipment
					MB15F73UL	For digital high-speed telecom- munications equipment
	100 MHz to 1.3GHz	RF Integer-N	64/65, 128/129		MB15F72UV	Small Package For digital high-speed telecommuni-
	50 MHz to 350 MHz	IF Integer-N	8/9, 16/17		WIDTOI 720V	cations equipment
					MB15F72UL	For digital high-speed telecommunications equipment
	100 MHz to 1.1GHz	RF Integer-N	64/65, 128/129		MD45F070I	For digital high-speed telecommuni-
	100 MHz to 1.1GHz	IF Integer-N	64/65, 128/129		MB15F07SL	cations equipment Low noise
		Integer-N Sigma-De	:Integer-N tech Ita:Sigma-Delta fr		0,	gy

• Dual Integer-N PLL

Part number	frequ	put iency I (Hz)	PLL		Divide ra	tio		Power supply current	Power save current	v	er su oltag (V)	pply e	Pack	age
	min	max	Туре	Prescaler	Program counter	Swallow counter	Referenc e counter	typ (mA)	typ (μ A)	min	typ	max	всс	TSSOP
MB15F74UV	2.0G 200M	4.0G 2.0G		RF : 64/65, 128/129 IF : 32/33, 64/65	Dinor	Dinomi	Dinory	6.5 2.5	0.1 0.1	2.7	3.0	3.6	18P	_
MB15F73UV	200M 50M	2.25G 600M		RF: 64/65, 128/129 IF: 8/9, 16/17	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	2.0 1.2	0.1 0.1	2.4	2.7	3.6	18P	_
MB15F72UV	100M 50M	1.3G 350M		RF: 64/65, 128/129 IF: 8/9, 16/17				1.5 1.0	0.1 0.1	2.4	2.7	3.6	18P	_
MB15F78UL	400M 100M	2.6G 1.2G		XX : 32/33, 64/65 XX : 16/17, 32/33	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	2.8 1.7	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F76UL	2.0G 100M	6.0G 1.5G	Integer	RF: 16/17, 32/33 (Fixed part 4 division) IF: 4/5, 8/9 (Fixed part 4 division)	13011	Binary 5bit 0 to 31	Binary 14bit 3 to 16383	6.2 2.3	0.1 0.1	2.5	3.0	3.6	20P	_
MB15F74UL	2.0G 200M	4.0G 2.0G		RF: 64/65,128/129 IF: 32/33,64/65		Dinami	Dinami	6.5 2.5	0.1 0.1	2.7	3.0	3.6	20P	_
MB15F73UL	200M 50M	2.25G 600M		RF: 64/65,128/129 IF: 8/9,16/17	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	2.0 1.2	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F72UL	100M 50M	1.3G 350M		RF: 64/65,128/129 IF: 350M: 8/9,16/17			12 12 10000	1.5 1.0	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F07SL	100M 100M			64/65,128/129 64/65,128/129	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	5.5 5.5	0.1 0.1	2.5	3.0	3.6	16P	16P

Package: P - Plastic



• Single Sigma-Delta Fractional-N PLL

Part number	Input frequency band (Hz)		PLL Type	Divide ratio		Power supply save current current		Power supply voltage (V)			Package		
	min	max	Туре	Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	typ (μ A)	min	typ	max	всс
MB15E65UV	100 M	2.0 G	Sigma-	16/17	Binary 8 bit 9 to 255	Binary 4 bit 0 to 15	Binary 6 bit 1 to 63	4.9	0.1	2.7	3.0	3.3	18P
MB15E64UV	100 M	3.5 G	Delta	16/17	Binary 8 bit 9 to 255	Binary 4 bit 0 to 15	Binary 6 bit 1 to 63	4.9	0.1	2.7	3.0	3.3	18P

Package: P - Plastic

• Single Sigma-Delta Fractional-N PLL (RF) & Integer-N PLL (IF)

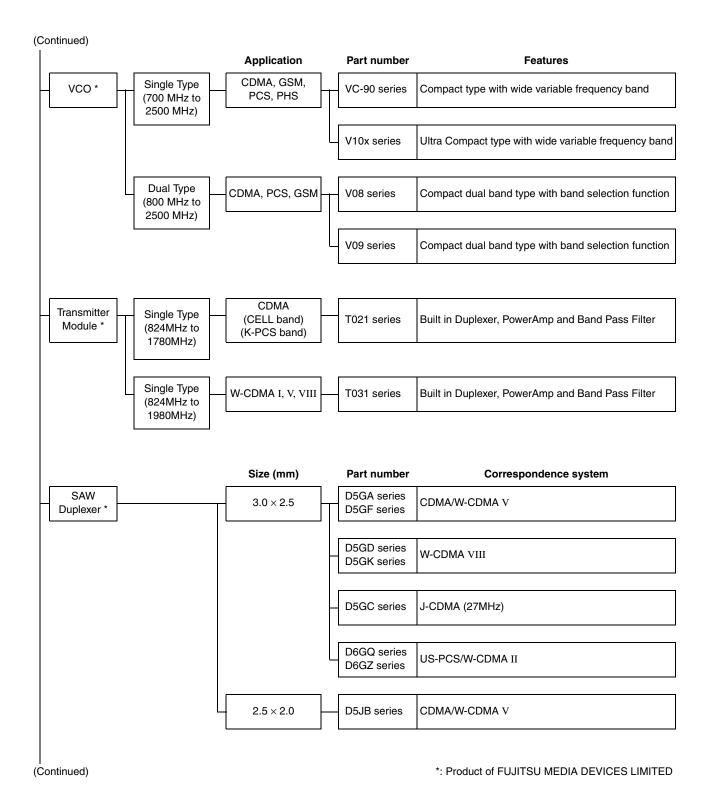
	Part number	frequ	out ency (Hz)	PLL Type	Divide ratio				Power supply current	save current	Power supply voltage (V)			Package
		min	max	Турс	Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	typ (μ A)	min	typ	max	всс
	MB15F63UL		2.0G 600M	Sigma -Delta, Integer -N	RF : 16/17, 20/21,	Binary 7bit 5 to 127(RF) Binary 11bit 3 to 2047(IF)	Rinary 7hit	Binary 6bit 1 to 63(RF) Binary 14 bit 3 to 16383(IF)	6.1 1.4	0.1 0.1	2.7	3.0	3.3	20P

Package: P - Plastic

• Specific power saving communication

Part number	Application	Frequency band	Functions	Power supply current	save current	Power su voltage		(V)	Раскаде
		(MHz)		typ (mA)	typ (μA)	min	typ	max	LQFP
MB15H121	Telemeter telecontroller security	430	Prescaler divide ratio 8/9 PA, ΣΔPLL, FSK-MOD, LNA, MIXER, LIMAMP, RSSI, FSK-DEM, VCO TANK circuit (internal)	6.7 (PLL) 23.0 (TX) 5.0 (RX)	0.3	2.2	2.5	2.8	48P

Package: P - Plastic



VCO

Part number	Functions	Application	Frequency (MHz)	Power supply voltage (V)	Package Typ. (mm)
VC-90 series		CDMA, GSM, PCS,	700 to 2500	2.5 to 3.3	$5.0\times4.0\times1.55$
V10x series	Voltege Controlled Oscillator	PHS	700 to 2300	2.5 10 5.5	$4.5 \times 3.2 \times 1.5$
V08 series	- voitege Controlled Oscillator	CDMA, PCS, GSM	800 to 2500	2.8	$5.5 \times 4.8 \times 1.8$
V09 series		CDIVIA, PC3, G3IVI	800 10 2500	2.0	$5.0\times4.0\times1.4$

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Transmitter Module

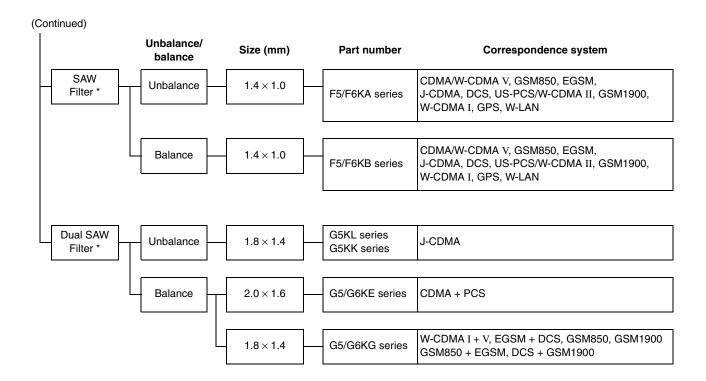
Part number	Functions	Application	Frequency (MHz)	Power supply voltage (V)	Package Typ. (mm)
T021 series	Built in Duplexer, PowerAmp	CDMA (CELL band)	824 to 849	3.4	8.0 × 5.0 × 1.4
1021 361163	and Band Pass Filter	1750 to 1780	5.4	0.0 × 5.0 × 1.4	
	D. ili in Danielana Barrantana	W-CDMA I	1920 to 1980		
T031 series	Built in Duplexer, PowerAmp and Band Pass Filter	W-CDMA V	824 to 849	3.4	$7.0\times4.0\times1.2$
			880 to 915		

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SAW Duplexer for Mobile Communication System

Correspondence system	Size (mm)	Part Number	Remarks
	3.0 × 2.5	FAR-D5GA-881M50-D1AA	Two types of package are available
CDMA/W-CDMA V	3.0 × 2.5	FAR-D5GF-881M50-D1FB	Rx: Balanced 100 ohm
	2.5 × 2.0	FAR-D5JB-881 M50-D3AA	Two types of package are available
W-CDMA VIII	3.0 × 2.5	FAR-D5GK-942M50-D1KF	-
W-CDIVIA VIII	3.0 × 2.5	FAR-D5GD-942M50-D1DF	Rx: Balanced 100 ohm
J-CDMA (27MHz)	3.0 × 2.5	FAR-D5GC-911M50-D1CA	-
US-PCS/W-CDMA II	3.0 × 2.5	FAR-D6GQ-1G9600-D1QBQ	Rx: Balanced 100 ohm
US-1 US/VV-UDIVIA II	3.0 × 2.5	FAR-D6GZ-1G9600-D1ZA	Two types of package are available

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SAW Filter for Mobile Communication System

Correspondence system	Transmission/ Reception	Size (mm)	Part number	Remarks
			FAR-F5KA-836M50-D4DF	Unbalanced
	Transmission	1.4 × 1.0	FAR-F5KB-836M50-B4ER	Balanced 100 ohm output
			FAR-F5KB-836M50-B4EG	Balanced 200 ohm output
CDMA/W-CDMA V			FAR-F5KA-881M50-D4DB	Unbalanced
	Reception	1.4 × 1.0	FAR-F5KB-881M50-B4ED	Balanced 100 ohm output
	·		FAR-F5KB-881M50-B4EJ	Balanced 200 ohm output
0011050	Transmission	1.4 × 1.0	FAR-F5KA-836M50-D4CM	Unbalanced
GSM850	Reception	1.4 × 1.0	FAR-F5KB-881M50-B4EA	Balanced 150 ohm output
	Transmission	1.4 × 1.0	FAR-F5KA-897M50-D4DC	Unbalanced
EGSM	- ·		FAR-F5KA-942M50-D4DD	Unbalanced
	Reception	1.4 × 1.0	FAR-F5KB-942M50-B4EB	Balanced 150 ohm output
			FAR-F6KA-1G5754-L4AA	Unbalanced
			FAR-F6KA-1G5754-L4AJ	Unbalanced
GPS	-	1.4 × 1.0	FAR-F6KA-1G5754-L4AB	Ultra low insertion loss, Unbalanced
			FAR-F6KB-1G5754-B4GE	Balanced 100 ohm output, Low loss
			FAR-F6KB-1G5754-B4GU	Balanced 100 ohm output, High Attenuation
	Tuenenienien	4 4 4 0	FAR-F6KA-1G7675-D4CT	Unbalanced
	Transmission	1.4 × 1.0	FAR-F6KB-1G7675-B4GF	Balanced 200 ohm input
W-CDMA IX	Reception	1.4 × 1.0	FAR-F6KA-1G8625-D4DH	Unbalanced
			FAR-F6KB-1G8625-B4GT	Balanced 100 ohm input
			FAR-F6KB-1G8625-B4GG	Balanced 200 ohm input
	Transmission	1.4 × 1.0	FAR-F6KA-1G7475-D4CY	Unbalanced
DCS	Reception	1.4 × 1.0	FAR-F6KA-1G8425-D4CK	Unbalanced
	neception	1.4 × 1.0	FAR-F6KB-1G8425-B4GA	Balanced 150 ohm output
	Transmission	1.4 × 1.0	FAR-F6KA-1G8800-L4AF	Unbalanced
US-PCS/W-CDMA II	Reception	1.4 × 1.0	FAR-F6KA-1G9600-D4DQ	Unbalanced, high attenuation
	neception	1.4 × 1.0	FAR-F6KB-1G9600-B4GP	Balanced 100 ohm output
GSM1900	Reception	1.4 × 1.0	FAR-F6KA-1G9600-D4CR	Unbalanced
G3W1900	neception	1.4 × 1.0	FAR-F6KB-1G9600-B4GB	Balanced 150 ohm output
	Transmission	1.4 × 1.0	FAR-F6KA-1G9500-D4DG	Unbalanced
W-CDMA I	Iransmission	1.4 × 1.0	FAR-F6KB-1G9500-B4GJ	Balanced 100 ohm input
VV-CDIVIA I	Reception	1.4 × 1.0	FAR-F6KA-2G1400-D4CG	Unbalanced
	neception	1.4 × 1.0	FAR-F6KB-2G1400-B4GC	Balanced 100 ohm output
TD-SCDMA	-	1.4 × 1.0	FAR-F6KA-2G0175-D4DR	Unbalanced
			FAR-F6KA-2G4418-D4CU	Unbalanced
W-LAN	-	1.4 × 1.0	FAR-F6KA-2G4418-A4VA	Unbalanced, high power handling
			FAR-F6KB-2G4418-B4GL	Balanced 100 ohm output
	•			(Product of FUJITSU MEDIA DEVICES LIMITED

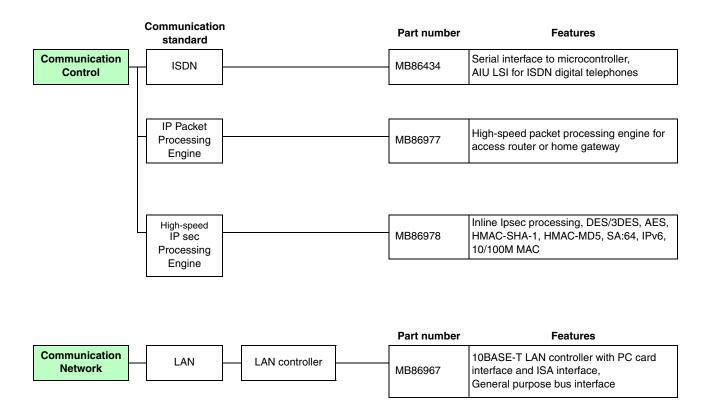
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SAW Dual Filter for Mobile Communication System

Correspondence system	Transmission /Reception	Size (mm)	Part number	Remarks	
EGSM + DCS	Reception	1.8 × 1.4	FAR-G6KG-1G8425-Y4SA	Balanced 150 ohm output, Opposite type of Filter position is available.	
EGSM + GSM850	Reception	1.8 × 1.4	1.8 × 1.4 FAR-G5KG-942M50-Y4SD Balanced 150 ohm output, Opposite type of Filter position		
GSM850 + GSM1900	Reception	1.8 × 1.4	FAR-G6KG-1G9600-Y4PB	Balanced 150 ohm output, Opposite type of Filter position is available.	
GSM1900 + DCS	Reception	1.8 × 1.4	FAR-G6KG-1G9600-Y4SC	Balanced 150 ohm output, Opposite type of Filter position is available.	
CDMA + US-PCS	Reception	2.0 × 1.6	FAR-G6KE-1G9600-Y4LY	Balanced 100 ohm output, Opposite type of Filter position is available.	
J-CDMA	Transmission	1.8 × 1.4	FAR-G5KL-911M50-D4XC	Unbalanced, 1 input/2 output	
J-CDIVIA	Transmission	1.8 × 1.4	FAR-G5KK-911M50-D4KE	Unbalanced, 2 input/2 output	
W-CDMA I + V	Transmission	1.8 × 1.4	FAR-G6KG-1G9500-Y4PG	Balanced 200 ohm input	
VV-CDIVIA I + V	Reception	1.8 × 1.4	FAR-G6KG-2G1400-Y4SH	Balanced 200 ohm output	

(Product of FUJITSU MEDIA DEVICES LIMITED)

Communication Control/Communication Network



Communication Control/Communication Network

Communication Control

ISDN

Part number	Functions	Communication standard	Power supply voltage (V)	Package QFP
MB86434	AIU LSI for ISDN digital telephones, Internal CODEC, DTMF tones, service tone, and ringer tone	-	+5 ± 5%	64P

Package: P - Plastic

IP Packet Processing Engine

Part number	Functions	Power supply voltage (V)	Package LQFP
MB86977	Enable to process following functions with hardware. IP Packet Forwarding Packet Filtering NAT PPPoE and more. Supports QoS, DMZ, IPv6 and more. 10/100M MAC (Conforms to IEEE802.3)	3.3 ± 0.3 1.8 ± 0.15	208P

Package: P - Plastic

High Speed IP sec Processing Engine

Part number	Functions	Power supply voltage (V)	Package FBGA
MRX697X	Inline Ipsec processing, DES / 3DES,AES,HMAC - SHA-1,HMAC-MD5,SA:64,IPv6,10 / 100M MAC	3.3 ± 0.3 1.8 ± 0.15	337P 288P

Package: P - Plastic

■ Communication Network

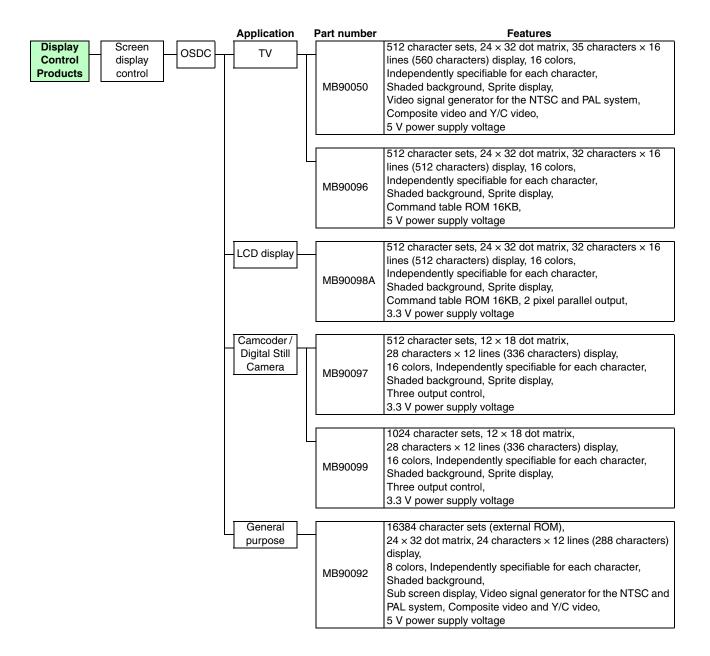
LAN

Part number	Functions	Communication standard	Power supply voltage (V)	Package LQFP
MIRKHUL/	10BASE-T Ethernet controller with PC card interface, ISA bus interface and General purpose bus interface	Conforms to IEEE 802.3	+5 ± 5%	100P

Note: Ethernet is a registered trademark of XEROX Corporation of the USA.

Package: P - Plastic

Display Control Products



Display Control Products

■ Display Control Products

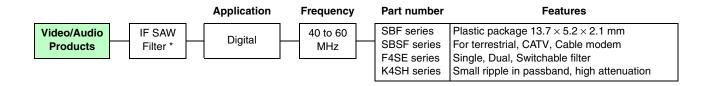
Screen Display Control

OSDC (On-Screen Display Controller)

	<u>.</u>	Number	Character		RGB	Analog	Sync	Power		Р	ackag	je				
Part number	Character generator	of character set	dot	Screen size	digital output	(video) output	signal	supply voltage (V)	SH- DIP	SOP	QFP	SSOP	FLGA			
MB90050	Internal ROM			35 characters × 16 lines	6bit (16 color selection in 64 colors)	Composite Video and Y/C video	NTSC PAL	+5 ±10%	1	ı	48P	_				
MB90096		- Internal ROM	512	24 × 32	32 characters				+5 ±10%	28P	28P	_	_	_		
MB90098A			Internal ROM	- Internal BOM	ternal BOM		× 16 lines	4bit	Unavailable	Unavailable Unavailable	+3.3	ĺ	28P	_	_	_
MB90097				12 × 18	28 characters	(16 colors)	Oriavallable	Oriavallable	±0.3	1	1	_	20P	_		
MB90099		1024	12 × 10	× 12 lines				+2.4 to +3.6	ĺ	ĺ	_	20P	20P			
MB90092	External ROM	16384 (Max.)	24 × 32	24 characters × 12 lines	3bit (8 colors)	Composite Video and Y/C video	NTSC PAL	+5 ±10%	_	_	80P	_	_			

Package: P - Plastic

Video/Audio Products



*: Product of FUJITSU MEDIA DEVICES LIMITED

Video/Audio Products

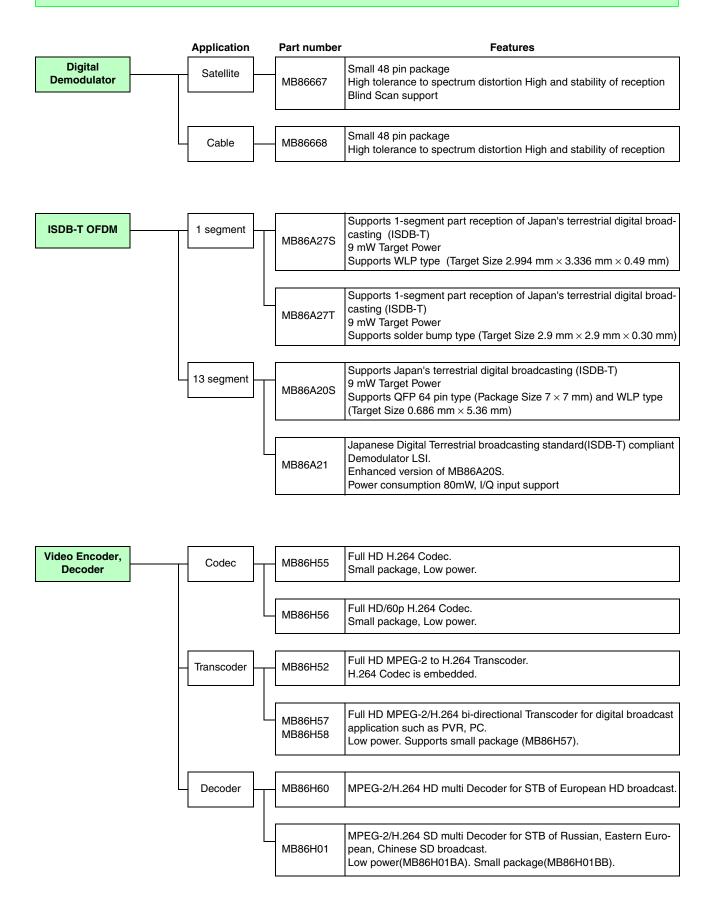
■ Video/Audio Products

IF SAW Filter for Digital

(Product of FUJITSU MEDIA DEVICES LIMITED)

Applicable types	Center frequency (MHz)	3 dB Bandwidth (MHz)	Part number
DAB	38.912	1.50	SBF0402GPL
	44.000	1.70	SBF0402JPL
000	44.000	1.70	FAR-F4SE-44M000-A011
OOB	44.000	2.60	FAR-F4SE-44M000-H0A6
	44.000	4.00	FAR-F4SE-44M000-H0A3
	36.000	8.10	FAR-F4SE-36M000-A005
	36.125	6.10	FAR-F4SE-36M125-A001
	36.125	7.00	SBF0407BPL
	36.125	8.10	SBF0408KPL
	43.750	6.00	FAR-F4SE-43M750-A006
	43.750	6.00	FAR-F4SE-43M750-H0AB
	44.000	5.35	FAR-F4SE-44M000-H0AG
	44.000	5.37	FAR-F4SE-44M000-H0A4
	44.000	5.42	FAR-F4SE-44M000-H0A8
CATV/TV	44.000	5.49	FAR-F4SE-44M000-H0A1
(US/Euro)	44.000	5.50	FAR-F4SE-44M000-H0AH
	44.000	6.00	FAR-F4SE-44M000-H0A9
	44.000	6.12	FAR-F4SE-44M000-H0A2
	44.000	6.20	FAR-F4SE-44M000-H0AA
	44.000	8.00	SBF0408LPL
	47.250	6.20	FAR-F4SE-47M250-H0AC
	36.000	6.4/7.4 (Switchable)	FAR-K4SH-36M000-L0E1
	36.000	7.0/7.9 (Switchable)	SBSF03ABPL
	36.125	6.0/7.9 (Switchable)	FAR-K4SH-36M125-F001
	36.125	7.0/7.9 (Switchable)	SBSF03AAPL
	57.000	5.30	FAR-F4SE-57M000-H0JC
CATV/TV	57.000	5.40	FAR-F4SE-57M000-H0J9
(Japan)	57.000	5.62	FAR-F4SE-57M000-H0J6
	57.000	5.62	FAR-F4SE-57M000-H0J3
	35.230	8.00	FAR-F4SE-35M230-A013
TV tuner	36.125	6.90	FAR-F4SE-36M125-H0E8
	36.125	7.60	FAR-F4SE-36M125-H0E5
TV/STB	36.125	7.90	FAR-F4SE-36M125-H0E7

Demodulator Products/ISDB-T OFDM/Video Encoder, Decoder



Demodulator Products/ISDB-T OFDM/Video Encoder, Decoder

Demodulator Products

Satellite

Part number	Function	Power supply voltage (V)	Package
i art namber	T dilotion	Tower suppry voltage (v)	QFP
MB86667	QPSK demodulator	1.65 to 1.95	48P
IVIDO0007	DVB-S and DSS support	3.0 to 3.6	401

Cable

	Part number	Function	Power supply voltage (V)	Package
	i art number	T diletion	Tower supply voltage (v)	QFP
	MB86668	QAM demodulator	1.65 to 1.95	48P
	MIDOOOOO	DVB-C support	3.0 to 3.6	401

Package: P - Plastic

■ ISDB-T OFDM

1 Segment

Part number	Function	Power supply voltage (V)	Package		
raitiiuiiibei	Function	rower supply voltage (v)	Solder Bump	WLP	
MB86A27S	1 segment OFDM demodulator	1.2 (internal, analog)		42pin	
IVIDOUAZ/3	ISDB-T supports	1.8 to 2.8 (I/O), 2.8 (analog)	_		
MB86A27T	1 segment OFDM demodulator	1.2 (internal, analog)	48pin	_	
WIDOUAZ7 I	ISDB-T supports	1.8 to 2.8 (I/O), 2.8 (analog)	400111	-	

13 Segment

Part number	Function	Power supply voltage (V)	Pack	age
rait ilullibei	T unction	rower supply voltage (v)	LQFP	WLP
MB86A20S	13 segment OFDM demodulator ISDB-T supports	1.2 (internal, analog) 3.3 (I/O), 3.3 (analog)	64P	58P
MB86A21	13 segment OFDM demodulator ISDB-T supports	1.2 (internal, analog) 3.3 (I/O), 3.3 (analog)	64P	-

Package: P - Plastic

■ Video Encoder, Decoder

Codec

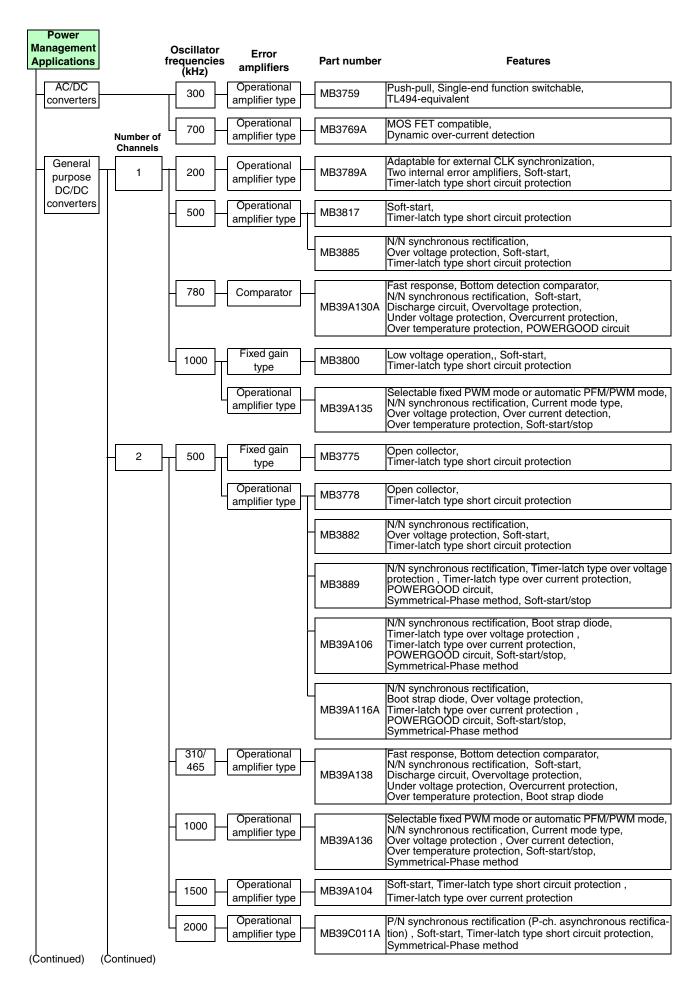
Part number	Function	Power consumption (mW)	Memory	Package FBGA
MB86H55	H.264 HP Level4.0 Codec Various Audio Codec	500	1piece 512Mbit	650pin
MB86H56	H.264 HP Level4.2 Codec 1920x1080/60 supports Various Audio Codec	700	FCRAM is embedded	15mm × 15mm

Transcoder

Part number	Function	Power	Memory	Package		
raitiidiibei	Tunction	consumption (W)	Wemory	FBGA	PBGA	
MB86H52	MPEG-2 to H.264 HD Transcode H.264 HP Level4.0 Codec Various Audio Codec	1.7	2 pieces 512Mbit DDR2-667	-	496pin 27mm × 27mm	
MB86H57	MPEG-2/H.264 bi-directional Transcode Audio Transcode		4 min on E4OMbit	650pin 15mm × 15mm	-	
MB86H58	H.264 HP Level4.0 Encode MPEG-2 MP@ML Encode Various Audio Codec MULTI2 decryption is embedded	1.0	1 piece 512Mbit FCRAM is embbeded	-	496pin 27mm × 27mm	

Decoder

Part number	Function	Power	Memory	Pack	rage
rait ilullibei	Tunction	consumption (W)	wiemory	FBGA	PBGA
MB86H60	ARM1176JZF-S(324MHz) MPEG-2 MP@HL Decode H.264 HP Level 4 Decode Various Audio Decode DVB descrambler is embedded	1 12	2 pieces 16bit DDR2-SDRAM 667MHz (256Mbit to 1Gbit)	-	484pin 27mm × 27mm
MB86H01BA	ARC Tangent-A4(202.5MHz) MPEG-2 MP@ML Decode	0.53 (with DAC)	1 piece 16bit DDR-SDRAM	-	256pin 27mm × 27mm
	H.264 MP Level 3 Decode MPEG-1/2 Layer I/II Audio Decode DVB descrambler is embbeded	0.31 (W/O DAC)	135MHz (128Mbit to 512Mbit)	240pin 10mm × 10mm	-



■ Power Management Applications

AC/DC Converters

Part number	Function	Switching circuit		Power	No. of	Operating oscillator	Reference	ce voltage	Package
Part number		Bipolar	FET	supply voltage (V)	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)	SOP
MB3759	PWM-type controllers Yes No +7 to +32		1	300	5	5.0	16P		
MB3769A	for AC/DC converters	Yes	Yes	+12 to +18	, I	700	J	2.0	16P

Packages: P - Plastic

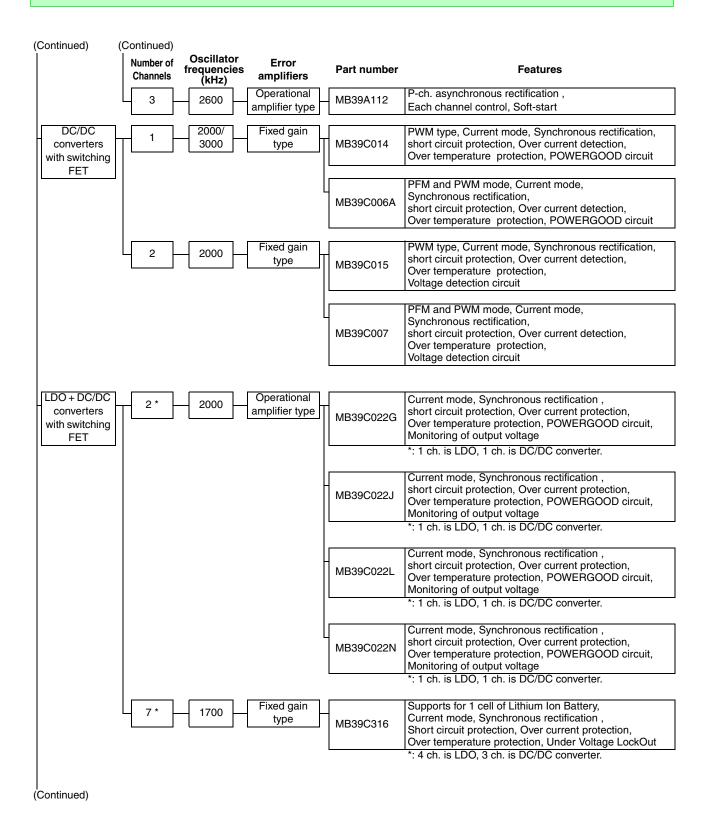
General Purpose DC/DC Converters

Part number	Function	Switching method	Power	No. of	Operating oscillator frequency	vo	erence Itage	Solutions		Packa	ge
		method	(V)	channels	(kHz) (Max.)	(V) (Typ.)	Precision (%)		SOP	SSOP	TSSOP
MB3789A			+3.0 to +18		200	2.5	4.0	Up conversion	-	16P	_
MB3817	PWM-type	Voltage mode	+2.5 to +18		500	1.5	2.0	Up conversion Down conversion Invert	_	16P	_
MB3885	controllers for DC/ DC converters	mode	+5.5 to +18			1.25	1.0	Down conversion	_	20P	_
MB3800	DO CONVENTORS		+1.8 to +15	1	1000	0.5	4.0	Up conversion	8P	8P	_
MB39A130A	PFM/PWM-type controllers for DC DC converters	Bottom detection comparator	+4.5 to		780	0.7 *	1.0	Down conversion	-	-	24P
MB39A135		Current mode	+25		1000	0.7	1.0	DOWN CONVENSION	_	_	16P
MB3775			+3.6 to			1.28	1.5	Up conversion Down conversion	16P	16P	_
MB3778			+18			2.46	2.0	Invert	16P	16P	_
MB3882	PWM-type controllers for DC/	Voltage	+5.5 to		500	1.25			-	24P	_
MB3889	DC converters	mode	+18		300	1.23			1	-	30P
MB39A106			+6.5 to			1.20			-	-	30P
MB39A116A			+18	2		1.00			-	-	30P
MB39A136	PFM/PWM-type controllers for DC/ DC converters	Current mode	+4.5 to +25	2	1000	0.7 *	1.0	Down conversion	-	-	24P
○MB39A138		Bottom detection comparator	+6 to +24		310/465	0.7/2.0			-	_	24P
MB39A104		Voltage	+7 to +19		1500	1.24			-	24P	_
MB39C011A		Voltage mode	+4.5 to +17		2000	1.0			-	-	16P

O: New product

*: Feadback Voltage

Packages: P - Plastic



General Purpose DC/DC Converters

		Switching	Power	No. of	Operating oscillator	Referen	ce voltage		Package
Part number	Function	method	SUDDIV	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)	Solutions	TSSOP
MB39A112	PWM-type controllers for DC/DC converters	Voltage mode	+7 to +25	3	2600	1.0/1.23	1.0	Down conversion	20P

Packages: P - Plastic

DC/DC converters with switching FET

Part nun		Function	Power	No. of	Operating oscillator	Referen	ce voltage	Output current		ng FET istance	Solutions	Pack	kage
Part Hull	iibei	runction	supply voltage (V)	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)	DC/DC (mA) (Max)		Nch MOS (Ω) (Typ)		QFN	SON
MB39C	014	PWM type DC/DC		1	2000/3200 (Fix)	1.20						_	10P
MB39C	015	converters	2	2	2000 (Fix)	1.30		800	0.3	0.2	Down conversion	24P	-
MB39C	AOUU	PFM/PWM type	+2.5 to +5.5	1	2000/3200 (Fix) 1.20	1.20	2.0					_	10P
MB39C	007	DC/DC converters		2	2000 (Fix)	1.30						24P	_

Packages: P - Plastic

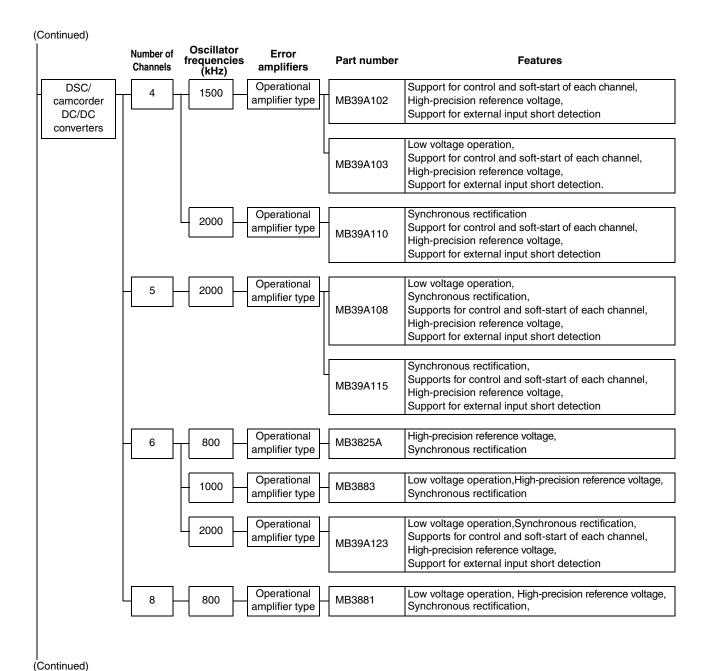
DC/DC converters with switching FET + LDO

		Power	No. of channels	Operating	Output	Output	Output current	Switching FET ON resistance		PSSR		Package
Part number	Function	supply voltage (V)		oscillator frequency (kHz)	voltage (V)	precision (%)	DC/DC (mA) (Max.)	Pch MOS (Ω) (Typ)	Nch MOS (Ω) (Typ)	(dB) (Typ)	Solutions	SON
Common condition	DC/DC converter			2000	0.8 to 4.5 (variable)	2.5	600	0.35	0.25	-		
○MB39C022G			1ch DC/DC + 1ch LDO		3.3 (Typ)					-70		
OMB39C022J	Low noise				2.85 (Typ) 1.8 (Typ)	0.5	000			-65	Down conversion	10P
OMB39C022L	LDO	+5.5				1.8	2.5 30	300	_	_	-60	1
OMB39C022N					1.2 (Typ)					-55		

O: New product Packages: P - Plastic

Power Management IC for Portable Products

	_	intro for rottable rroducts									
Part number	No. chan		Power supply	Switching			Output	features		Package	
Fart number	DCDC	LDO	voltage (V)	frequency (kHz)	Pin name	Output voltage (V)	FET	Output current (mA) (Max.)	Solutions	WL-CSP	
					DCDC1	1.2		800	Down conversion		
					DCDC2	1.825	Integrated	600	Down conversion		
			+2.7 to		DCDC3	3.3		650	Up/Down conversion		
MB39C316	3	4		1700	LDO1	2.875		200		49	
			+5.5	-	LDO2	1.225		260			
					LDO3	1.20/1.30	_	6.5	-		
					LDO4	2.925		84			

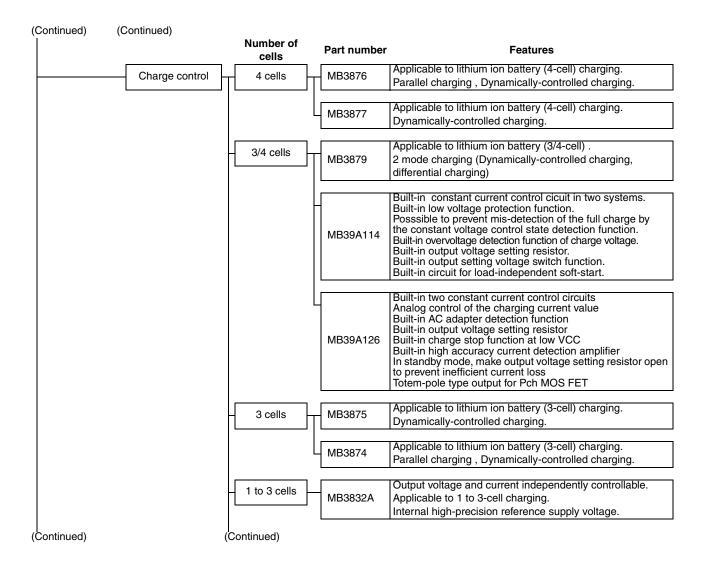


DSC/Camcorder DC/DC Converters

Part number	Function	Power	No. of	Operating oscillator	Referen	ce voltage	Solutions	Drive	F	Packag	е
Part number	Function	supply voltage (V)	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)	Solutions	circuit	LQFP	всс	TSSOP
MB39A102		+2.5 to +11		1500				Pch : 3, Nch : 1	_	32P	30P
MB39A103		+1.7 to +11	4	1000			Up conversion	Pch : 1, Nch : 3	_	32P	30P
MB39A110		+2.5 to +11			2.0		Down conversion Up/Down	Pch : 3, Nch : 1		_	38P
MB39A108		+1.7 to +11	т.	2000			conversion	Pch : 3, Nch : 2	_	40P	38P
MB39A115	PWM-type	71.7 10 711	5			1.0		Pch : 4, Nch : 1	_	40P	38P
MB3825A	controllers for DC/DC	+2.5 to +12		800	1.5	1.0	Down conversion	PNP:6	64P **	_	
MB3883	converters	+1.7 to +9	6	1000	2.5		Up conversion Down conversion Up/Down conversion	Pch : 2, Nch : 4	48P	48P	_
MB39A123		+1.7 to +11		2000 2.0		Up conversion Down conversion Up/Down conversion Invert	Pch : 4, Nch : 2	48P	48P	_	
MB3881		+1.8 to +13	8	800	2.5	1.0	Down conversion Up/Down conversion	Pch : 7, Nch : 1	64P *		

Packages: P - Plastic

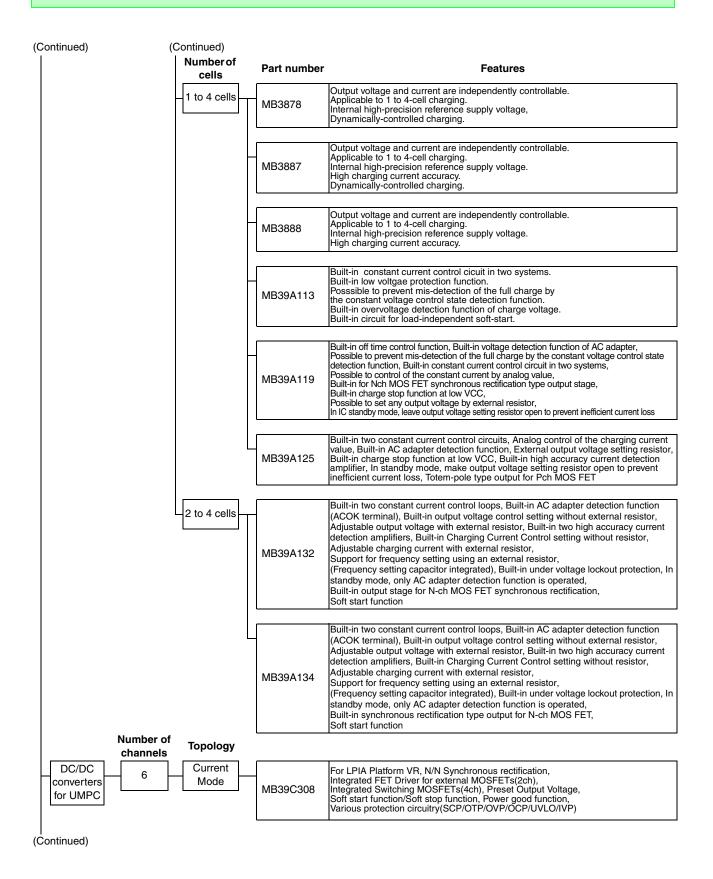
^{*: 0.4} mm pitch **: 0.4 mm pitch, 0.5 mm pitch



Charge control

		Power					Operating		ı	Package)																		
Part number	Function	supply	Output voltage	Pre	cision (%)	Number	fraguancy	Solutions																					
		voltage (V)	(V)	Ta = +25 °C	Ta = -30 to +85 °C	of cells	(kHz) (Max.)		SSOP	LQFP	QFN																		
MB3876		+7 to +25	16.8	±0.8	±1.0	4			24P	_	-																		
MB3877		+7 10 +25	10.0	±0.6	±1.0	4			24P	_	_																		
MB3879	1	+8 to +25	12.6/16.8				48P																						
IVID3079											12.3/16.4	±0.9	±1.1					401											
	Charge control				12 6/16 9	±0.5	±0.74 *	3/4	500	Down	24P	-	-																
140004400	DC/DC converters				17 to 195															12.0	12.0/10.0	±0.6	±0.80 *		500	conversion	24P	-	28P
MB3875								12.6	±0.8	±1.0	3			24P	-	_													
MB3874			12.0	±∪.0	±1. U	3			24P	-	-																		
MB3832A	-	+3.6 to +18	Any voltage level	±0.5	±1.0*	1 to 3			20P	-	-																		

^{* :} Ta = -10 to +85 °C Package: P-plastic



Charge control

Part number	Function	Power supply voltage (V)					Operating		Package		
			Output voltage (V)	Precision (%)		Number	oscillator frequency	Solutions			
				Ta = +25 °C	Ta = -30 to +85 °C	of cells	(kHz) (Max.)		SSOP	TSSOP	QFN
MB3878	Charge control DC/DC converters	+7 to +25	4.2 V/cell	±0.8	±1.0	1 to 4	500	Down conversion	24P	-	_
MB3887		+8 to +25		+0.6 -0.4	±0.74 * ¹				24P	-	_
MB3888			Any voltage level	±0.5					20P	_	_
			4.2 V/cell						24P	-	_
MRRAATIA							1000		-	_	28P
							500		24P	_	28P
MB39A132			4.0V/Cell, 4.2V/Cell, 4.35V/Cell, Any voltage level		±0.5 * ²	2 to 4	2000		-	-	32P
MB39A134			4.2V/Cell, 4.1V/Cell, Any voltage level		±0.7 * ¹				ı	24P	_

^{*1 :} Ta = -10 °C to +85 °C *2 : Ta = +25 °C to +85 °C

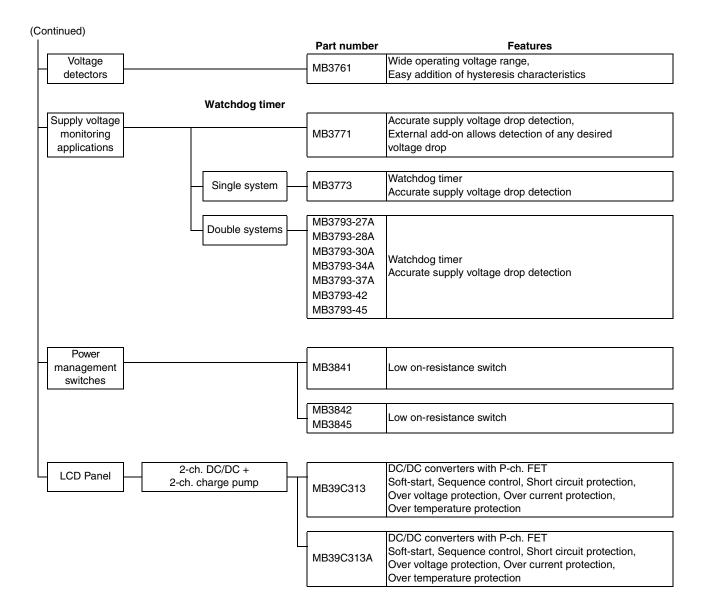
DC/DC converters for Ultra Mobile PC

Part number	Function	Input voltage (V)	Number of channels	Oscillator frequencies (kHz)		Outp		Package		
					Pin name	Preset output voltage (V)	FET	Drive or Output current (A) (Max)	Solutions	PFBGA
MB39C308	DC/DC converters for LPIA Platform VR	+5.5 to +12.6	6	700 (Fix)	CH1	5	External	2	Down conversion	208P
					CH2	3.3		4.5		
					СНЗ	1.8/1.5	Integrated	2.7		
					CH4	0.9/0.75		1.5		
					CH5	1.5		2.5		
					CH6	1.1/1.05		3.5		

LPIA=Low Power Intel Architecture®

Package: P-plastic

Package: P-plastic



Power Management Applications

Voltage Detectors

Part number	Function	Power supply voltage	Reference voltage	Package
T di t ildilibei	Tunction	(V)	(V) (Typ.)	SOP
MB3761	Voltage detector	+2.5 to +40	1.2	8P

Package: P - Plastic

Supply Voltage Monitoring Applications

Doub wassels as	Franklan	Power supply	Data ation walters (10)	Reset certified	Pacl	cage
Part number	Function	voltage (V)	Detection voltage (V)	voltage (V) (Typ.)	SOP	SSOP
MB3771	Supply voltage monitoring applications	+3.5 to +18	Any voltage level in		8P	-
	Supply voltage monitoring applications with watchdog timer	+3.5 to +16	addition to 4.2 V		8P	_
MB3793-27A	Ţ.	+4 (Max.)	2.7±0.07		8P	8P
MB3793-28A		+4 (Max.)	2.8±0.07		8P	-
MB3793-30A	Outside the second section of the second section of		3.0±0.07	0.8	8P	8P
MB3793-34A	Supply voltage monitoring applications with dual watchdog timer systems		3.4±0.08		8P	-
MB3793-37A	rith dual watchdog timer systems	+6 (Max.)	3.7±0.1		8P	-
MB3793-42			4.2±0.1		8P	-
MB3793-45			4.5±0.1		8P	-

Package: P - Plastic

Switching Applications

Part number	Function	Power supply	Number of	On-resistance	Drive current	Pack	cage
r art maniber	Tunction	voltage (V) (Max.)	channels	(Ω)	(A) (Max.)	SOP	SSOP
MB3841			1	0.045	2.0	8P	-
MB3842	ower management switch	5.5	2	0.1	0.6		20P
MB3845			2	0.1	0.0	_	201

Package: P - Plastic

LCD Panel

		Power					Outp	ut feature	s			Package		
Part number	Function	supply	Number of channels	Switching frequency kHz(Fix)	Pin name	Circuit type or solution	Error amplifier threshold voltage (V)	Precision (%)	Output voltage (V)		Output current (A)	TSSOP		
	2ch. DC/				Vlogic	Step down DC/DC	1.213	1.5	1.8 to 3.3	Integrated	1.5			
MB39C313	DC + 2ch.	+8 to	4	500/750	V _S	Step up DC/ DC	1.146	0.9	18.1 (Max)	-	1.5 * ¹	28P * ²		
	charge pump	+14			V _{GL}	Invert charge pump	0 ± 36mV	-	_	_	50mA			
	pamp				V _{GH}	Step up charge pump	1.213	2.1	_	_	50mA			
	2ch DC/	2ch. DC/	+8 to			Vlogic	Step down DC/DC	1.213	1.5	1.8 to 3.3	Integrated	1.5		
○MB39C313A	DC + 2ch.	+8 to		4	500/750	Vs	Step up DC/ DC	1.146	0.9	18.1 (Max)	integrated	1.5 * ¹	28P * ²	
	charge pump	charge +14		+14			V _{GL}	Invert charge pump	0 ± 36mV	-	_	_	100mA	
					V _{GH}	Step up charge pump	1.213	2.1		_	100mA			

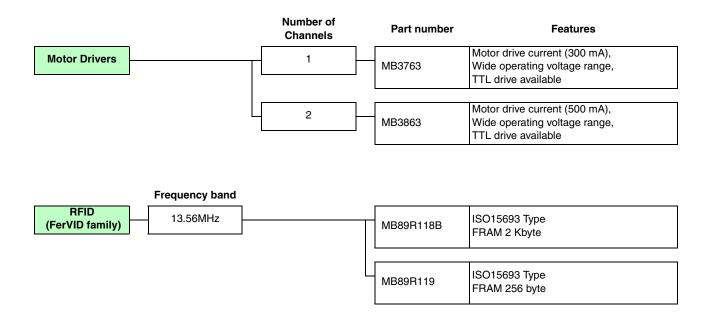
O: New product

*1: 12V input/15V output

*2: With exposed pad

Package: P - Plastic

Motor Drivers/RFID (FerVID family™)



Motor Drivers/RFID (FerVID family™)

Motor Drivers

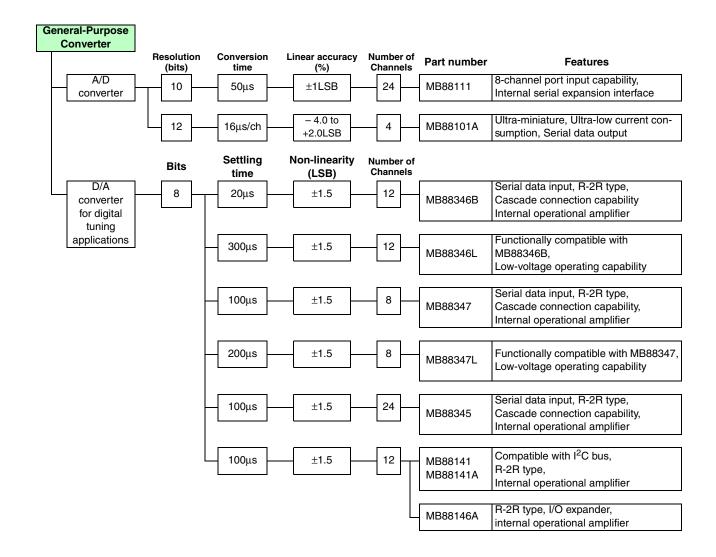
Part number	Function	Number of Channels	Output current (mA)	Power supply voltage (V)	Package SOP
MB3763	Reversible motor drivers	1	300	+4 to +18	8P
MB3863	neversible motor drivers	2	500	+4 to +36	20P

Package: P - Plastic

■ RFID (FerVID family™)

Part number	Frequency band	Interface	Transmission speed (Reader/Writer -> LSI)	Transmission speed (LSI -> Reader/Writer)	FRAM (byte)	Shipment form
MB89R118B	13.56MHz	ISO15693	26.48kbps (52.97kbps)	26.48kbps (52.97kbps)	2K	Wafer (With a golden Bump)
MB89R119	13.30WI12	ISO15693	26.48kbps (52.97kbps)	26.48kbps (52.97kbps)	256	Wafer (With a golden Bump)

General-Purpose Converter



General-Purpose Converter

■ General-Purpose Converter

A/D Converter

Part number	Function	Conversion	Conversion time	time Linearity			ı	Package)	
		method	(μs/ch) (Max.)	(Max.)	supply voltage (V)	DIP	SOP	SSOP	QFP	SH-DIP
MB88111	24-ch 10-bit A/D converter	Successive	50	±1 LSB	+3.5 to +5.5	_	_	_	44P	48P
MB88101A	4-ch 12-bit A/D converter	approximation	16 (at 5 V±10%)	-4.0 to +2.0 LSB	+3.3 to +5.5	16P	16P	16P	ı	_

Packages: P - Plastic

D/A Converter for Digital Tuning Applications

Part number	Function	Settling time	Power consumption	Non- linearity	Power supply voltage		Pac	kage	
i ait namber	Tunction	(μs) (Max.)	(mW) (Typ.)	error (LSB)	(V)	DIP	SOP	SSOP	QFP
MB88346B	12-ch 8-bit D/A converter (internal operational amplifier)	20	14		+5±10%	20P	20P	20P	_
MB88346L	12-ch 8-bit D/A converter (internal operational amplifier, low voltage operation)	300	5		+2.7 to +3.6	20P	20P	20P	-
MB88347	8-ch 8-bit D/A converter (internal operational amplifier)	100	9		+5±10%	16P	16P	16P	-
MB88347L	8-ch 8-bit D/A converter (internal operational amplifier, low voltage operation)	200	4.2	±1.5	+2.7 to +3.6	16P	16P	16P	-
MB88345	24-ch 8-bit D/A converter (internal operational amplifier)	100	27			_	_	_	32P
MB88141	12-ch 8-bit D/A converter (compatible with I ² C bus,		15		+5±10%	24P	24P	24P	-
MB88141A	internal operational amplifier)	100				∠ -f1	<u> </u>	<u>∠</u> -TI	_
	12-ch 8-bit D/A converter (I/O expander, internal operational amplifier)		14.5		Digital:+2.7 to +5.5 Analog:+5±10%	24P	-	24P	-

Package: P - Plastic

SD/SDHC card

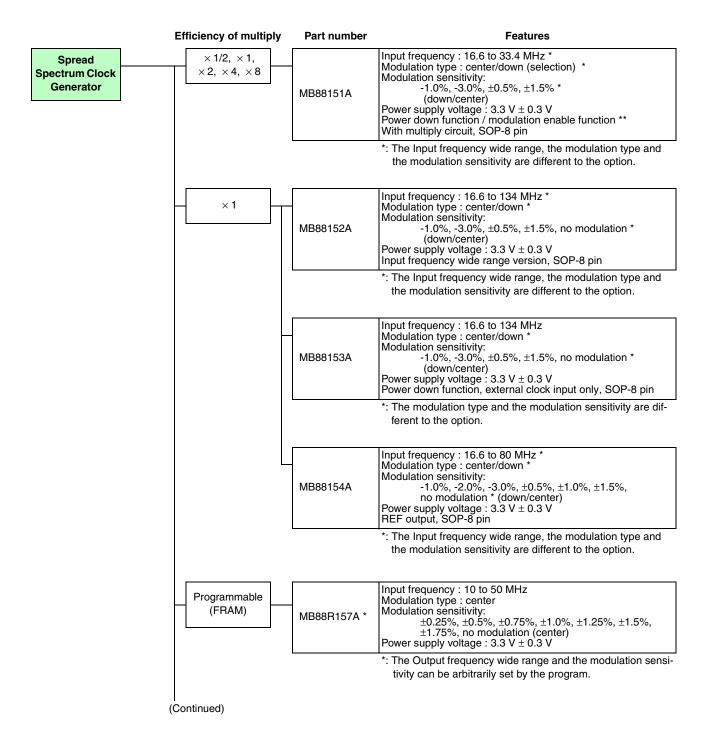
SD/SDHC card	SD/SDHC-ATA bridge LSI		The parallel AT -> SD/SDHC card bridge chip driver software is unnecessary.
			SD memory card physical specification Ver.2.0 support

SD/SDHC card

SD/SDHC card

Part number	Function	Power supply voltage (V)	Package FBGA
MSC1007	SDHC memory card support PIO 0-4 and ultra DMA mode 3 ATA-6 specification conforming Hardware protocol conversion of SD-IDE Boot from the SD/SDHC card	+3.0 to +3.6	100P

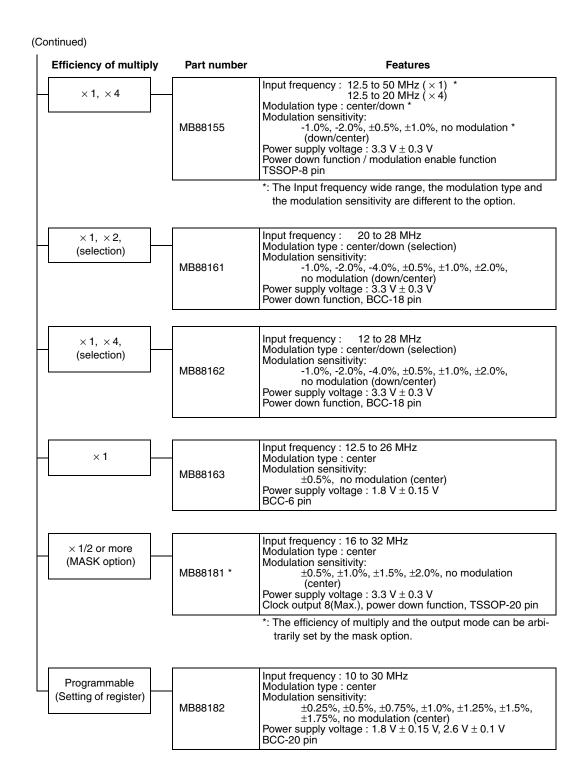
Package: P - Plastic



■ Spread Spectrum Clock Generator

		Power	Input	Efficiency of	Output	Modulation	Modulation		Package
Part number	Function	supply voltage	frequency (MHz)	multiply	frequency (MHz)	Туре	sensitivity	Other	SOP
MB88151A-100								PD function disable	
MB88151A-101				× 1	16.6 to 33.4			PD function enable	
MB88151A-200				_				PD function disable	
MB88151A-201			16.6 to 22.4	× 2	33.2 to 66.8		-1.0%, -3.0% (down)	PD function enable	
MB88151A-400			16.6 to 33.4	× 4	66.4 to	Down or center	$\pm 0.5\%, \pm 1.5\%$ (center) no modulation	PD function disable	
MB88151A-401				^4	133.6	(selection)	(no modulation setting is no PD	PD function enable	
MB88151A-500				1/0	0.04-10.7		product)	PD function disable	
MB88151A-501				× 1/2	8.3 to 16.7			PD function enable	
MB88151A-800			8.3 to 16.7	× 8	66.4 to			PD function disable	
MB88151A-801			0.0 10 10.7	^0	133.6			PD function enable	
MB88152A-100			16.6 to 40 33 to 67		16.6 to 40 33 to 67	Down	-1.0%, -3.0%		
MB88152A-110			40 to 80 66 to 134		40 to 80 66 to 134	Center	±0.5%, ±1.5%		
MB88152A-101	5041 mains		16.6 to 40		16.6 to 40	Down	-1.0%, -3.0% no modulation	_	
MB88152A-111	EMI noise reduction PLL	3.3 ± 0.3	33 to 67		33 to 67	Center	$\pm 0.5\%$, $\pm 1.5\%$ no modulation		8P
MB88152A-102	(SSCG)		40 to 80		40 to 80	Down	-1.0%, -3.0% no modulation		
MB88152A-112			66 to 134		66 to 134	Center	$\pm 0.5\%, \pm 1.5\%$ no modulation		
MB88153A-100						Down	-1.0%, no modulation		
MB88153A-101			16.6 to 40 66 to 134	× 1	16.6 to 40 66 to 134		-3.0%, no modulation	PD function	
MB88153A-110			33 to 67 40 to 80	^.1	33 to 67 40 to 80	Center	$\pm 0.5\%$, no modulation	enable	
MB88153A-111						o o mon	$\pm 1.5\%$, no modulation		
MB88154A-101			50 to 80		50 to 80				
MB88154A-102			33 to 67		33 to 67	Down	-1.0%, -2.0%, -3.0%, no modulation		
MB88154A-103			16.6 to 40		16.6 to 40			REF output	
MB88154A-111			50 to 80		50 to 80			enable	
MB88154A-112			33 to 67		33 to 67		$\pm 0.5\%, \pm 1.0\%, \\ \pm 1.5\%, no modulation$		
MB88154A-113			16.6 to 40	10	16.6 to 40	Center			
⊚MB88R157A			10 to 50	Programmable	1 to 134		$\pm 0.25\%, \pm 0.5\%, \\ \pm 0.75\%, \pm 1.0\%, \\ \pm 1.25\%, \pm 1.5\%, \\ \pm 1.75\%, \text{ no modulation}$	PD function enable, Programmable product	

©: Under development Package: P - Plastic (Continued)



(Continued)

		Power	Input		Output				an a	age							
Part number	Function	supply voltage (V)	frequency (MHz)	Efficiency of multiply	frequency (MHz)	Modulation Type	Modulation sensitivity	Other	TSSOP	ВСС							
MB88155-100			12.5 to 25		12.5 to 25		-1.0%, -2.0%	PD function									
MB88155-101			25 to 50		25 to 50	Down	no modulation	disable									
MB88155-102			12.5 to 25		12.5 to 25	- Down	1.09/ 0.09/	PD function									
MB88155-103			25 to 50	× 1	25 to 50		-1.0%, -2.0%	enable									
MB88155-110			12.5 to 25	X I	12.5 to 25		±0.5%, ±1.0%	PD function									
MB88155-111			25 to 50		25 to 50	Center	no modulation	disable	oD.								
MB88155-112	EMI noise reduction		12.5 to 25		12.5 to 25	Center	±0.5%, ±1.0%	PD function	OF-	_							
MB88155-113		3.3	25 to 50		25 to 50		±0.5%, ±1.0%	enable									
MB88155-400		± 0.3				Down	-1.0%, -2.0% no modulation	PD function disable									
MB88155-402				12.5 to 20	× 4	50 to 80	DOWII	-1.0%, -2.0%	PD function enable								
MB88155-410	PLL		12.5 10 20	× 4	^4	50 10 60	Center	$\pm 0.5\%$, $\pm 1.0\%$ no modulation	PD function disable								
MB88155-412	(SSCG)					Center	±0.5%, ±1.0%	PD function enable									
MB88161			12 to 28 (×1) 20 to 42 (×4)	×1, ×4, (selection)	12 to 28 (×1) 80 to 168 (×4)	Down/ Center (selection)	-1.0%, -2.0%, -4.0%, ±0.5%, ±1.0%, ±2.0%, no modulation	PD function enable	-	18P							
MB88162										12 to 28 (×1) 20 to 42 (×4)	\times 1, \times 4, (selectable)	12 to 28 (×1) 80 to 168 (×4)	Down/ Center (selectable)	-1.0%, -2.0%, -4.0%, ±0.5%, ±1.0%, ±2.0%, no modulation	PD function enable	-	18P
MB88163		1.8 ± 0.15	12.5 to 26	× 1	12.5 to 26		±0.5%, no modulation	-	-	6P							
MB88181		3.3 ± 0.3	16 to 32	× 1/2 or more *	8 to 166	Center	±0.5%, ±1.0%, ±1.5%, ±2.0%, no modulation	PD function enable, Clock output 8(Max.)	20P	-							
MB88182		1.8 V ± 0.15 V, 3.3 V ± 0.3 V	10 to 30	Programmable	8 to 100		$\pm 0.25\%, \pm 0.5\%, \\ \pm 0.75\%, \pm 1.0\%, \\ \pm 1.25\%, \pm 1.5\%, \\ \pm 1.75\%, \\ \text{no modulation}$	Programmable product	-	20F							

^{*:} The efficiency of multiply and the output mode can be arbitrarily set by the mask option.

Package: P - Plastic

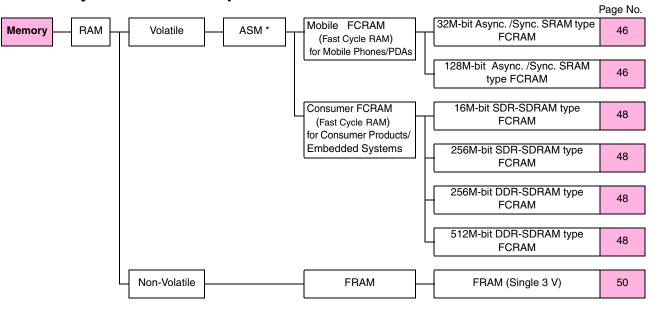
SSCG Simple Evaluation Board

	Part number		Remarks
	MB88151AEB01-100	MB88151A-100 mounted	
	MB88151AEB01-101	MB88151A-101 mounted	
	MB88151AEB01-200	MB88151A-200 mounted	
	MB88151AEB01-201	MB88151A-201 mounted	
MB88151A	MB88151AEB01-400	MB88151A-400 mounted	
VIDOOTSTA	MB88151AEB01-401	MB88151A-401 mounted	
	MB88151AEB01-500	MB88151A-500 mounted	
	MB88151AEB01-501	MB88151A-501 mounted	
	MB88151AEB01-800	MB88151A-800 mounted	
	MB88151AEB01-801	MB88151A-801 mounted	
	MB88152AEB01-100	MB88152A-100 mounted	
	MB88152AEB01-110	MB88152A-110 mounted	
MB88152A	MB88152AEB01-101	MB88152A-101 mounted	
VID00132A	MB88152AEB01-111	MB88152A-111 mounted	
	MB88152AEB01-102	MB88152A-102 mounted	
	MB88152AEB01-112	MB88152A-112 mounted	
	MB88153AEB01-100	MB88153A-100 mounted	
MB88153A	MB88153AEB01-101	MB88153A-101 mounted	
VIDOO I DOA	MB88153AEB01-110	MB88153A-110 mounted	
	MB88153AEB01-111	MB88153A-111 mounted	
	MB88154AEB01-101	MB88154A-101 mounted	
	MB88154AEB01-102	MB88154A-102 mounted	
MB88154A –	MB88154AEB01-103	MB88154A-103 mounted	An oscillator, oscillation stable capacity
	MB88154AEB01-111	MB88154A-111 mounted	and a power supply line are required.
	MB88154AEB01-112	MB88154A-112 mounted	
	MB88154AEB01-113	MB88154A-113 mounted	
	MB88155EB01-100	MB88155-100 mounted	
	MB88155EB01-101	MB88155-101 mounted	
	MB88155EB01-102	MB88155-102 mounted	
	MB88155EB01-103	MB88155-103 mounted	
	MB88155EB01-110	MB88155-110 mounted	
AD001EE	MB88155EB01-111	MB88155-111 mounted	
MB88155	MB88155EB01-112	MB88155-112 mounted	
	MB88155EB01-113	MB88155-113 mounted	
	MB88155EB01-400	MB88155-400 mounted	
	MB88155EB01-402	MB88155-402 mounted	
	MB88155EB01-410	MB88155-410 mounted	
	MB88155EB01-412	MB88155-412 mounted	
MB88161	MB88161EB01	MB88161 mounted	
MB88162	MB88162EB01	MB88162 mounted	
MB88163	MB88163EB01	MB88163 mounted	
MB88R157	MB88R157EB01	MB88R157 mounted *	
	MB88182EB01-1A	MB881821A mounted	
MD004.00	MB88182EB01-2A	MB881822A mounted	
MB88182	MB88182EB01-1B	MB881821B mounted	
	MB88182EB01-2B	MB881822B mounted	

^{*:} Hardware or software for writing is required.

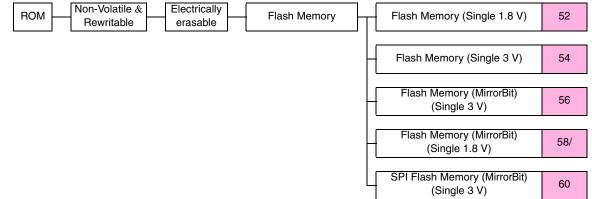
Memory Product Line-up

Memory Product Line-up



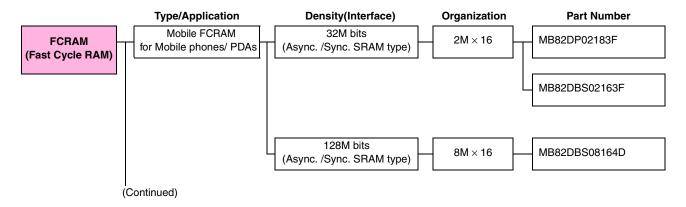
*: ASM =Application Specific Memory FCRAM is a trademark of Fujitsu Microelectronics Limited.

SPANSION™ Products



MirrorBit is a trademark of Spansion Inc.

FCRAM™ (Fast Cycle RAM) (1)



FCRAM is a trademark of Fujitsu Microelectronics Limited.

FCRAM[™] (Fast Cycle RAM) (1)

■ Mobile FCRAM (Fast Cycle RAM)

• 32M-bit Async. /Sync. SRAM Type FCRAM

*1, *2, *3

	Part Number	Initial					Current		
Organization (W × b)		Access Time Max. (ns) *4	Page Mode Access Time Max. (ns)	Burst Mode Frequency Max. (MHz)	Burst Clock Access Time Max. (ns)	Operating (mA)	Standby (μA)	Power Down (μA)	Supply Voltage (V)
0M v 16	MB82DP02183F-65L	65	20	N/A	N/A	30	120	10	2.6 to 3.1
2M × 16	MB82DBS02163F-70L	70	20	83	8 * ⁵	30	120	10	1.7 to 1.95

- *1: Compliant with COSMORAM spec
- *2: MB82DP02183F : with Page mode MB82DBS02163F : with SDR Burst mode & Page mode
- *3: Shipping form: Wafer, 71-pin FBGA package
- *4: At asynchronous operation
- *5: At RL = 5, 6

• 128M-bit Async. /Sync. SRAM Type FCRAM

*1, *2

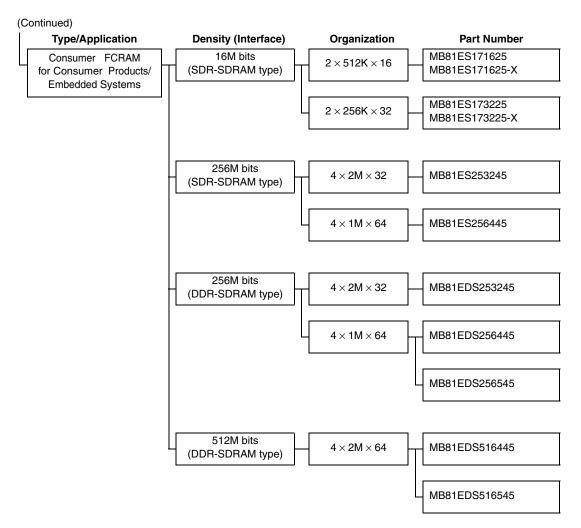
		Initial	Page Mode		Burst Clock	Supply	Current	t Max.		
Organization (W × b)	Part Number	Access Time Max. (ns) *3	Access Time Max. (ns)	Burst Mode Frequency Max. (MHz)	Access Time Max. (ns)	Operating (mA)	Standby (μA)	Power Down (µA)	Supply Voltage (V)	
$8M \times 16$	MB82DBS08164D-70L	70	N/A	77	6 * ⁴	35	200 * ⁵	10	1.7 to 1.95	

- *1: Compliant with COSMORAM spec, with SDR Burst mode
- *2: Shipping form: Wafer

Package support for mass production is T.B.D.

- *3: At asynchronous operation
- *4: At RL = 6
- *5: T_A <u>≤</u> +40 °C

FCRAM[™] (Fast Cycle RAM) (2)



FCRAM is a trademark of Fujitsu Microelectronics Limited.

FCRAM™ (Fast Cycle RAM) (2)

Consumer FCRAM (Fast Cycle RAM)

• 16M-bit SDR-SDRAM Type FCRAM

*1, *2

Organization		Clock	Clock Period	Access Time	Supply Curr	Supply	
(Bank × W × b)	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) *4	Operating (mA)	Standby (mA)	Voltage (V)
	MB81ES171625-12	85	11.7	10.2	30	1	1.65 to 1.95
$2\times512K\times16$	MB81ES171625-15	66.7	15	12	30	1	1.65 to 1.95
	MB81ES171625-15-X * ³	66.7	15	12	30	1	1.65 to 1.95
	MB81ES173225-12	85	11.7	10.2	30	1	1.65 to 1.95
2 × 256K × 32	MB81ES173225-15	66.7	15	12	30	1	1.65 to 1.95
	MB81ES173225-15-X * ³	66.7	15	12	30	1	1.65 to 1.95

- *1: Single Data Rate SDRAM Interface
- *2: Shipping form: Wafer
- *3: Extended operating temperature
- *4: Access Time = t_{AC}
 *5: Operating current is I_{DD1} (1 bank active) and Standby current is I_{DD2P} (Power

• 256M-bit SDR-SDRAM Type FCRAM

*1, *2, *3

Organization		Clock	Clock Period	Access Time	Supply Cur	Supply Voltage		
(Bank × W × b)	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) * ⁴	Operating (mA)	Standby (mA)	(V)	
$4\times2M\times32$	MB81ES253245	166	6	6	75	5	1.7 to 1.95	
$4 \times 1M \times 64$	MB81ES256445	166	6	6	75	5	1.7 to 1.95	

- *1: Single Data Rate SDRAM Interface
- *2: Operating temp.: Tj = -10 to +125 °C
 *3: Shipping form: Wafer
- *4: Access Time = t_{AC}

256M-bit DDR-SDRAM Type FCRAM

*1, *2, *3

Organization		Clock	Clock Period	Access Time	Supply Cur	Supply Voltage		
(Bank × W × b)	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) *4	Operating (mA) *5	Standby (mA)	(V)	
$4 \times 2M \times 32$	MB81EDS253245	216	4.6	6	235	5	1.7 to 1.95	
4 × 1M × 64	MB81EDS256445	216	4.6	6	300	5	1.7 to 1.95	
	MB81EDS256545 *6	216	4.6	6	300	5	1.7 to 1.95	

- *1: Double Data Rate SDRAM Interface
- *2: Operating temp.: Tj = -10 to +125 $^{\circ}$ C
- *3: Shipping form: Wafer
- *4: Access Time = t_{AC}
 *5: Operating current is IDD4R (at burst read)
- *6: with special function capability

512M-bit DDR-SDRAM Type FCRAM

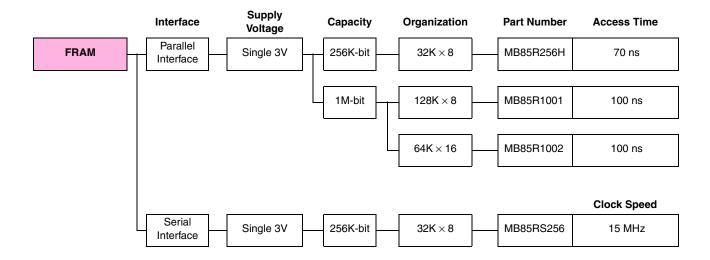
*1, *2, *3

Organization		Clock	Clock Period	Access Time	Supply Cur	Supply Voltage		
(Bank × W × b)	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) *4	Operating (mA) *5	Standby (mA)	(V)	
4 × 0M × 64	MB81EDS516445	216	4.6	6	300	9	1.7 to 1.9	
$4 \times 2M \times 64$	MB81EDS516545 *6	216	4.6	6	300	9	1.7 to 1.9	

- *1: Double Data Rate SDRAM Interface
- *2: Operating temp.: Tj = -10 to +125 °C
 *3: Shipping form: Wafer

- *4: Access Time = t_{AC}
 *5: Operating current is IDD4R (at burst read)
- *6: with special function capability

FRAM (Ferroelectric RAM)



FRAM (Ferroelectric RAM)

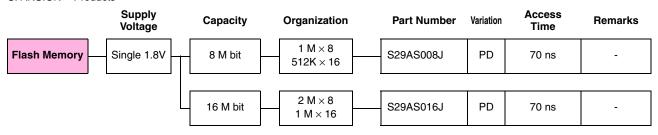
FRAM

Interface	Organization	Organization (W × b)	Access Time	Cycle Clock Time Speed		V _{CC} Current		Supply	Operating Temperature	Packages		
			Max. (ns)	Min. (ns)		Operating (mA)	Standby (μA)	Voltage (V)	Range T _A (°C)	SOP	тѕор	FBGA
Parallel	32K × 8	MB85R256H	70	150	=	5	5	2.7 to 3.6	-40 to +85	28P	28P	-
Parallel	128K×8	MB85R1001	100	150	-	10	10	3.0 to 3.6	-40 to +85	-	48P	-
Parallel	64K×16	MB85R1002	100	150	_	10	10	3.0 to 3.6	-40 to +85	-	48P	48P
Serial	32K × 8	MB85RS256	-	_	15	5	3	3.0 to 3.6	-20 to +85	8P	-	-

Pakage : P – Plastic

Flash Memory (Single 1.8V)

SPANSION™ Products



Flash Memory (Single 1.8V)

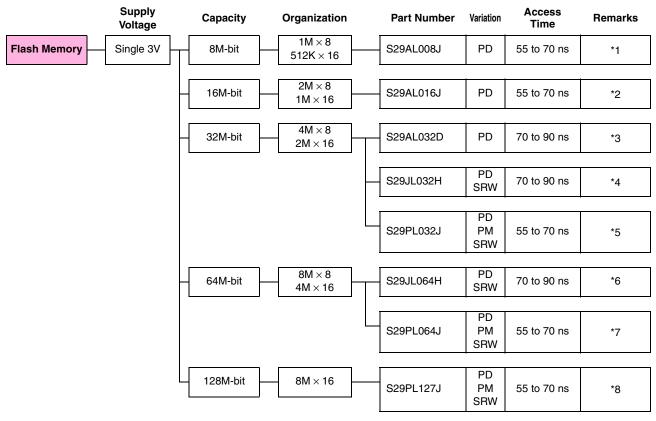
 $\mathsf{SPANSION^{\mathsf{TM}}}\ \mathsf{Products}$

■ Flash memory (Single 1.8V)

		Access	Cycle	V _{CC} Current			Operating	Packages	
Organization (W × b)	Part Number	Time Max. (ns)	Max. Time Read St		Standby Mode (μA)	Supply Voltage (V)	Temperature Range T _A (°C)	TSOP	FBGA
1 M×8 512 K×16	S29AS008J70	70	70	16 (f = 5 MHz)	5	1.65 to 1.95	-40 to +85	48	48
2 M × 8 1 M × 16	S29AS016J70	70	70	16 (f = 5 MHz)	5	1.65 to 1.95	-40 to +85	48	48

Flash Memory (Single 3V)





Variation

PD: Automatic sleep mode

PM: Page mode

SRW: Simultaneous Read / Write operation (Read-while-program or Read-

while-Erase)

MirrorBit is a trademark of Spansion Inc.

```
*1: (16Kbytes × 1sectors) + (8Kbytes × 2sectors) + (32Kbytes × 1sector) + (64Kbytes × 15sectors)
*2: (16Kbytes × 1sectors) + (8Kbytes × 2sectors + (32Kbytes × 1sector) + (64Kbytes × 31sectors)
*3: (16Kbytes × 1sectors) + (8Kbytes × 2sectors + (32Kbytes × 1sector) + (64Kbytes × 61sectors)
*4: (8Kbytes × 8sectors) + (64Kbytes × 63sectors)
*5: (2KWord × 16sectors) + (16KWord × 31sectors)
*6: (8Kbytes × 16sectors) + (64Kbytes × 126sectors)
*7: (2KWord × 16sectors) + (16KWord × 63sectors)
*8: (2KWord × 16sectors) + (16KWord × 127sectors)
```

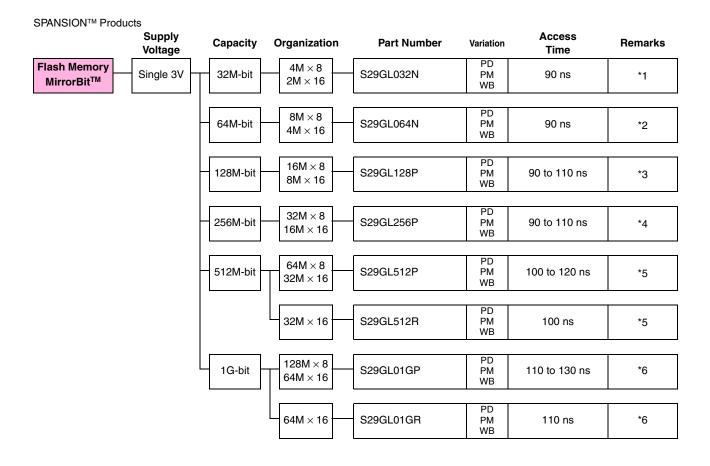
Flash Memory (Single 3V)

 $\mathsf{SPANSION^{\mathsf{TM}}}\ \mathsf{Products}$

■ Flash memory (Single 3V)

		Access	Ovele	V _{CC} Cu	rrent		Operating	Pack	ages
Organization (W × b)	Part Number	Time Max. (ns)	Cycle Time Min. (ns)	Read (mA)	Standby Mode (μA)	Supply Voltage (V)	Temperature Range T _A (°C)	TSOP	FBGA
1M × 8	S29AL008J55	55	55	12	5	3.0 to 3.6	-40 to +85	48	48
512K × 16	S29AL008J70	70	70	(f = 5 MHz)	5	2.7 to 3.6	-40 to +125	40	40
$2M \times 8$	S29AL016J55	55	55	12	5	3.0 to 3.6	-40 to +85	48	48
1M×16	S29AL016J70	70	70	(f = 5 MHz)	3	2.7 to 3.6	-40 to +125		64
	S29AL032D70	70	70	16	5	2.7 to 3.6	-40 to +85	40, 48	48
	S29AL032D90	90	90	(f = 5 MHz)	3	2.7 10 0.0	40 to +03	40, 40	40
	S29JL032H70	70	70	16	5	2.7 to 3.6	-40 to +85	48	_
$4M\times 8$	S29JL032H90	90	90	(f = 5 MHz)	3	2.7 10 0.0	40 to +03	70	
2M × 16	S29PL032J55	55	55						
	S29PL032J60	60	60	30	5	2.7 to 3.6	-45 to +85	_	48
	S29PL032J65	65	65	(f = 5 MHz)					56
	S29PL032J70	70	70						
	S29JL064H70	70	70	16	5	2.7 to 3.6	-40 to +85	48	_
	S29JL064H90	90	90	(f = 5 MHz)	Ŭ	2.7 10 0.0	40 10 100	40	
$8M \times 8$	S29PL064J55	55	55						
4M × 16	S29PL064J60	60	60	30	5	2.7 to 3.6	-45 to +85	_	48
	S29PL064J65	65	65	(f = 5 MHz)		2.7 10 0.0	45 to +05		56
	S29PL064J70	70	70						
	S29PL127J55	55	55			2.7 to 3.6			
8M × 16	S29PL127J60	60	60	30	5	2.7 10 0.0	-45 to +85	56	50
OIVI A 10	S29PL127J65	65	65	(f = 5 M⊔z)	lz) 5	2.7 to 3.6	-40 10 700	30	30
	S29PL127J70	70	70			1.65 to 1.95			

Flash Memory (MirrorBit™) (Single 3 V)



Variation

PM: Page mode WB: Write buffer

PD: Automatic sleep mode

MirrorBit is a trademark of Spansion Inc.

- *1: Uniform sector model : 32Kword (64Kbytes) × 64sectors
 Boot sector model : 32Kword (64Kbytes) × 63sectors + 4Kword (8Kbytes) × 8sectors
- *2: Uniform sector model : 32Kword (64Kbytes) × 128sectors
 Boot sector model : 32Kword (64Kbytes) × 127sectors + 4Kword (8Kbytes) × 8sectors
- *3: Sector structure 64Kword (128Kbytes) × 128sectors
- *4: Sector structure 64Kword (128Kbytes) × 256sectors
- *5: Sector structure 64Kword (128Kbytes) \times 512sectors
- *6: Sector structure 64Kword (128Kbytes) × 1024sectors

S29512GR and S29GL01GR: Please contact to sales representatives on the detail schedule.

Flash Memory (MirrorBit™) (Single 3 V)

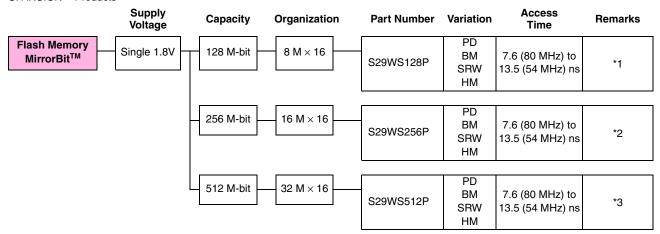
SPANSION™ Products ■ Flash memory (MirrorBit) (Single 3V)

		Access	Cycle	V _{CC} Cu	rrent		Operating	Pack	ages
Organization (W × b)	Part Number	Time * Max. (ns)	Time Min. (ns)	Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T _A (°C)	TSOP	FBGA
$4M \times 8$ $2M \times 16$	S29GL032N90	90 (25)	90	30 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	48 56	48 64
$8M \times 8$ $4M \times 16$	S29GL064N90	90 (25)	90	30 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	48 56	48 64
	S29GL128P90	90 (25)	90			3.0 to 3.6	0 to +85 -40 to +85		
$16M \times 8$ $8M \times 16$	S29GL128P10	100 (25)	100	55 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56	64
	S29GL128P11	110 (25)	110			2 10 0.0	10 10 100		
	S29GL256P90	90 (25)	90			3.0 to 3.6	0 to +85 -40 to +85		
$32M \times 8$ $16M \times 16$	S29GL256P10	100 (25)	100	55 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56	64
	S29GL256P11	110 (25)	110				10 10 100		
	S29GL512P10	100 (25)	100			3.0 to 3.6	0 to +85 -40 to +85		
$64M \times 8$ $32M \times 16$	S29GL512P11	110 (25)	110	55 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56	64
	S29GL512P12	120 (25)	120			2 10 0.0	10 10 100		
32M × 16	S29GL512R10	100 (25)	100	45 (f = 5 MHz)	100	3.0 to 3.6	0 to +85 -40 to +85	56	64
	S29GL01GP11	110 (25)	110			3.0 to 3.6	0 to +85 -40 to +85		
$128M \times 8$ $64M \times 16$	S29GL01GP12	120 (25)	120	55 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56	64
	S29GL01GP13	130 (25)	130						
64M × 16	S29GL01GR11	110 (25)	110	45 (f = 5 MHz)	100	3.0 to 3.6	0 to +85 -40 to +85	56	64

Access Time:() page access

Flash Memory (MirrorBit™) (Single 1.8V)

SPANSION™ Products



Variation

PD: Automatic sleep mode

BM: Burst mode

SRW: Simultaneous Raad/Write operation

(Read-while-program or Read-while-Erase)

HM: Hand Shake Mode

*1 : 16 Kword \times 8sectors + 64 Kword \times 126sectors *2 : 16 Kword \times 8sectors + 64 Kword \times 254sectors *3 : 16 Kword \times 8sectors + 64 Kword \times 510sectors

MirrorBit is a trademark of Spansion Inc.

Flash Memory (MirrorBit™) (Single 1.8V)

 $\mathsf{SPANSION^{\scriptscriptstyle\mathsf{TM}}}\,\mathsf{Products}$

■ Flash memory (MirrorBit) (Single 1.8V)

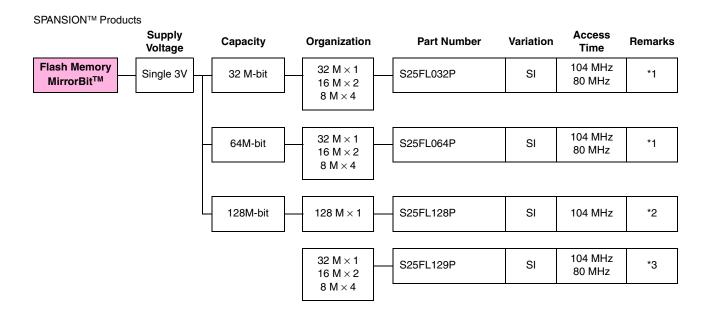
		Access	Burst	V _{CC} Cu	rrent		Operating	Packages
Organization (W × b)	Part Number	Time Max. (ns)	Speed (MHz)	Read (mA)	Standby Mode (μA)	Supply Voltage (V)	Temperature Range T _A (°C)	FBGA
	S29WS128P0LBxW	80 * ¹ 80/13.5 * ²	54	39 * ³				
8 M×16	S29WS128P0PBxW	80 * ¹ 80/11.2 * ²	66	43 * ³	70	1.70 to 1.95	-25 to +85	84
0 IVI × 10	S29WS128P0SBxW	80 *1 80/9.0 * ²	80	48 * ³	70	1.70 to 1.95		04
	S29WS128PABBxW	80 * ¹ 80/7.6 * ²	108	54 * ³				
	S29WS256P0LBxW	80 * ¹ 80/13.5 * ²	54	39 * ³	- 70	1.70 to 1.95	-25 to +85	
16 M × 16	S29WS256P0PBxW	80 * ¹ 80/11.2 * ²	66	43 * ³				84
10 W × 10	S29WS256P0SBxW	80 * ¹ 80/9.0 * ²	80	48 * ³				04
	S29WS256PABBxW	80 * ¹ 80/7.6 * ²	108	54 * ³				
	S29WS512P0LBxW	80 * ¹ 80/13.5 * ²	54	36 * ³				
22 M v 16	S29WS512P0PBxW	80 * ¹ 80/11.2 * ²	66	43 * ³	70	1.70 to 1.95	-25 to +85	84
32 M × 16	S29WS512P0SBxW	80 * ¹ 80/9.0 * ²	80	48 * ³	70	1.70 to 1.95	-20 10 +00	04
	S29WS512PABBxW	80 * ¹ 80/7.6 * ²	108	54 * ³				

^{*1:} Asynchronous access time

^{*2:} Synchronous delay time/burst access time

^{*3:} At burst read Continuous mode (Max.)

Serial Peripheral Interface (MirrorBit™) (Single 3V)



^{*1 :} Uniform 64KB sectors (Top or bottom boot sector : 32 $\, imes$ 4 K bytes parameter block)

Variation SI: Serial interface

MirrorBit is a trademark of Spansion Inc.

^{*2 : 256} KB \times 64 sectors or 64 KB \times 256 sectors

 $^{^{\}star}3$: Uniform 64KB sectors (Top or bottom boot sector : 32×4 K bytes parameter block) or Uniform 256KB \times 64 Sector

Serial Peripheral Interface (MirrorBit™) (Single 3V)

 $\mathsf{SPANSION^{\scriptscriptstyle\mathsf{TM}}}\,\mathsf{Products}$

■ Flash memory (MirrorBit) (Single 3V)

Organization (W × b)	Part Number	Clock	V _{CC} Current		Supply	Operating Temperature	Packages	
		speed (MHz)	Read (mA)	Standby Mode (μA)	Voltage (V)	Range T _A (°C)	SOIC	SON
32 M × 1	S25FL032P	104	25 (f = 104MHz)	200	2.7 to 3.6	-40 to +85	SOIC8	USON
16 M × 2 8 M × 4		80	38 (f = 80MHz)	200	2.7 to 3.6	-40 to +85	SOIC16	WSON
64 M×1	- S25FL064P	104	25 (f = 104MHz)	200	2.7 to 3.6	-40 to +85	SOIC16	WSON
32 M × 2 16 M × 4		80	38 (f = 80MHz)	200	2.7 to 3.6	-40 to +85	301010	WOON
128 M × 1	S25FL128P	104	22 (f = 104MHz)	200	2.7 to 3.6	-40 to +85	SOIC16	WSON
128 M × 1	S25FL129P	104	25 (f = 104MHz)	200	2.7 to 3.6	-40 to +85	SOIC16	WSON
64 M × 2 32 M × 4		80	38 (f = 80MHz)	200	2.7 to 3.6	-40 to +85	SOIC16	WSON

Products Scheduled to be out of Production

The productions listed below are scheduled to go out of production. If you are considering the use in the new applications, select the other series of products

FCRAM

Part number	Description		
MB82D01181E-60L	16 Mbit Async. SRAM Type FCRAM		
MB82DS01181E-70L			
MB82DP02183C-65L	32 Mbit Async. SRAM Type FCRAM		
MB82DP02183E-65L	oz ivibit Asyric. Shawi Type i Chaivi		
MB82DBS02163C-70L	32 Mbit Async./Sync. SRAM Type FCRAM		
MB82DBS02163E-70L	oz Mibit Async./3yric. Shalivi Type i Chalivi		
MB82DP04183C-65L			
MB82DP04183D-65L	64 Mbit Async. SRAM Type FCRAM		
MB82DP04184E-65L			
MB82DBS04163C-70L			
MB82DBS04163D-70L	64 Mbit Async./Sync. SRAM Type FCRAM		
MB82DBS04164E-70L			
MB82DBS08164C-70L	128 Mbit Async./Sync. SRAM Type FCRAM		
MB82DBS04314C-70L			

■ Flash Memory

Parallel Flash Memory (3.0V)

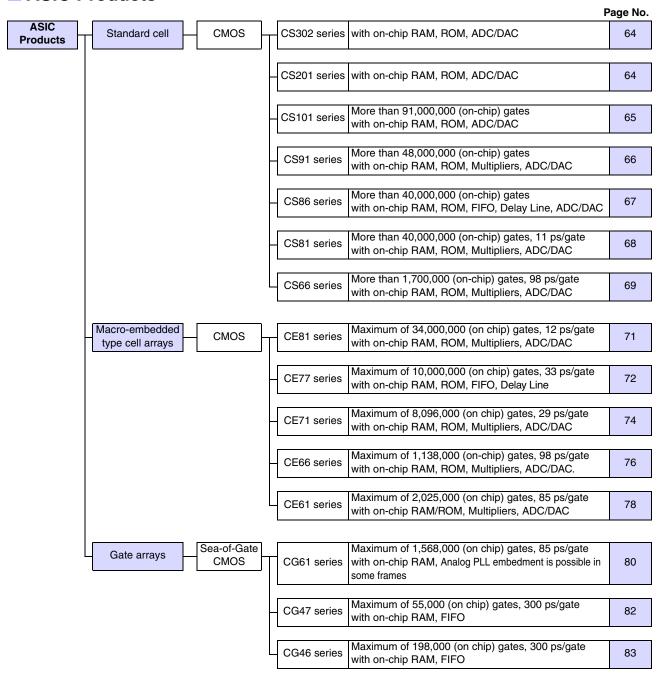
Part number		Description		
	S29AL004D	4Mbit, Access Time(ns): 70/90, Vcc: 2.7-3.6V		

Serial Flash Memory (MirrorBit) (3.0V)

Part number	Description	
S25FL040A	4Mbit, Clock Speed(MHz): 50, Vcc: 2.7-3.6V	
S25FL008A	8Mbit, Clock Speed(MHz): 50, Vcc: 2.7-3.6V	
S25FL016A	16Mbit, Clock Speed(MHz): 50, Vcc: 2.7-3.6V	
S25FL032A	32Mbit, Clock Speed(MHz): 50, Vcc: 2.7-3.6V	
S25FL064A	64Mbit, Clock Speed(MHz): 50, Vcc: 2.7-3.6V	

ASIC Product Line-up

ASIC Products



CS302 Series

Features

Technology : 40 nm Si-gate CMOS

: Maximum 11-metal layers. Extreme Low-K (ultra low permittivity) material is used for

dielectric inter-layers.

: Three different types of core transistors (low leak, standard and high speed) can be

used on the same chip.

Supply voltage :+1.1V \pm 0.1V

Junction temperature range :-40 °C to +125 °C

Support various cell sets (from low power versions to high speed versions)

It supports energy-saving mode, multi mode SRAM.

Compiled cells (RAM, ROM, others) Support low-consumption technology

Support ultra high speed (up to 10 Gbps) interface macros

Special interfaces (LVDS, SSTL, others)

Supports boundary SCAN

Supports use of industry standard libraries Supports use of industry standard tools.

Short-term development using a physical prototyping tool.

One pass design using a physical synthesis tools.

Hierarchical design environment for supporting large-scale circuits.

Supports Signal Integrity, EMI noise reduction

Supports static timing sign-off

Improve timing convergence by using Statistical Static Timing Analysis (SSTA).

Design For Manufacturing (DFM) enables stable product-supply and reduced variation

Package lineup: FBGA, PBGA, TEBGA, FC-BGA

Note: Some items are in preparation.

CS201 Series

Features

Technology : 65 nm Si-gate CMOS

6 to 12 layers of metal wiring. Ultra Low-K (low permittivity) material is used for

dielectric inter-layers.

Three different types of core transistors (low leak, standard and high speed) can be used

on the same chip.

Supply voltage : +0.9V to +1.3V (A wide range is supported.)

Junction temperature range : -40 °C to +125 °C Reduced chip sized realized by I/O with pad.

Supports a wide range of cell sets (from low power versions to high speed versions)

IP macros : CPU (ARM11, ARM9, ARM7TDMI), DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others

Compiled cells (RAM/ROM and others)

It supports energy-saving mode, multi mode SRAM. It supports energy-saving technology "CoolAdjust"* Supports large capacity memory (1T-SRAM-Q) High-speed interface macro (up to 10 Gbps) Special interfaces (LVDS, SSTL and others)

Supports use of industry standard libraries (. LIB)
Uses industry standard tools and supports the optimum tools for the application.

High reliability design estimation in the early stage of physical design realized by physical prototyping tool.

Layout synthesis with optimized timing realized by physical synthesis tools.

Hierarchical design environment for supporting large-scale circuits.

High accuracy design environment considering dynamic drop in power supply voltages, signal noise, delay penalty, and crosstalk.

I/O design environment (power line design, assignment and selection of I/Os, package selection) considering noise.

Supports static timing sign-off

Improved timing settling by introducing Statistical Timing Analysis (SSTA).

Steady product supply and countermeasure for diffusion by introduction of DFM

Supports memory (RAM/ROM) BIST

Supports boundary SCAN
Supports LOGIC BIST

Supports transition delay test

Package lineup : TEBGA, FBGA, PBGA, FC-BGA

*: "CoolAdjust" is a generic name of Fujitsu Microelectronics's energy-saving technology

Note: Some items are in preparation.

CS101 Series

Features

Optimum gate count : Maximum of 91,000,000 gates

Technology : 90 nm Si-gate CMOS

6 to 10 layers of metal wiring. Low-K (low permittivity) material is used for all

dielectric inter-lavers.

Three different types of core transistors (low leak, standard, and high speed) can be used

on the same chip.

Supply voltage : +0.9V to +1.3V (A wide range is supported.) Junction temperature range : -40 °C to +125 °C

Gate delay time tpd = 12 ps (1.2 V, Inverter, F/O = 1)

Pd = 2.7 nW/MHz/BC (1.2 V, Inverter, F/O = 1)Gate power consumption

Reduced chip sized realized by I/O with pad.

Supports a wide range of cell sets (from low power versions to high speed versions)

Compliance with industry standard design rules enables non-Fujitsu commercial macros to be easily incorporated. : CPU (ARM9, ARM7TDMI), DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others IP macros

Compiled cells (RAM/ROM and others) High-speed interface macro (up to 10 Gbps) Special interfaces (LVDS, SSTL_2 and others) Supports use of industry standard libraries (. LIB)

Uses industry standard tools and supports the optimum tools for the application.

High reliability design estimation in the early stage of physical design realized by physical prototyping tool.

Layout synthesis with optimized timing realized by physical synthesis tools.

Hierarchical design environment for supporting large-scale circuits.

High accuracy design environment considering drop in power supply voltages, signal noise, delay penalty, and crosstalk.

I/O design environment (power line design, assignment and selection of I/Os, package selection) considering noise.

Supports static timing sign-off

Supports memory (RAM/ROM) BIST

Supports boundary SCAN Supports LOGIC BIST Supports transition delay test

Package lineup: TEBGA, FBGA, PBGA, FC-BGA

Note: Some items are in preparation.

CS91 Series

Features

Optimum gate count : Maximum of 48,000,000 gates

Technology : 0.11 µm Si-gate CMOS, 5- to 8-layer wiring (Copper is used as wire material),

Low-k Inter-layer material

(Inter-layer material that has low permittivity)

Supports 8 types of cell sets that differ in speed, integration, and power consumption.

These cell sets can be mixed on a chip.

Supply voltage : $+1.2 \text{ V} \pm 0.1 \text{ V}$ Junction temperature range : -40 to +125 °C

Gate delay time : tpd = 16 ps (1.2 V, Inverter, F/O = 1) Gate power consumption : Pd = 6.6 nW/MHz (1.2 V, Inverter, F/O = 1)

High-speed interface macro (up to 10 Gbps)

Special interfaces: P-CML, LVDS, PCI, USB, SSTL, HSTL, T-LVTTL, and others

Buffer cells for crystal oscillation circuits.

IP macros : CPU (ARM9, ARM7TDMI), DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others

Compiled cells (RAM/ROM/multiplier and others)

Uses industry standard tools and supports the optimum tools for the application.

Short-term development using a physical prototyping tool.

Hierarchical design environment for supporting large-scale circuits.

Supports Signal Integrity, EMI noise reduction

Supports High resolution RC extraction base delay calculation environment

Supports optimization environment of power supply wire

Supports static timing sign-off

Supports memory (RAM/ROM) BIST

Supports boundary SCAN Supports LOGIC BIST Supports transition delay test

Package lineup: FC-BGA (Max. 2116 pin), EBGA, HQFP, FBGA and others

Note: Some items are in preparation.

CS86 Series

Features

Optimum gate count : Maximum of 40,000,000 gates

Technology : 0.18 μm Si-gate CMOS, 5- to 6-layer wiring

Supports three types of internal cell sets (ultra high-speed, standard, low-leak)

Capable of integrating a mixture of standard transistor cell and ultra high-speed process/cell, and mixture of standard transistor cell and low leak process/cell on a single chip

Supply voltage : $\pm 1.8 \text{ V} \pm 0.15 \text{V}$ to $\pm 1.1 \text{V} \pm 0.1 \text{V}$

Gate delay time : tpd = 88 ps (standard : 1.8 V, 2NAND, F/O = 2, standard load)

tpd = 70 ps (ultra high-speed : 1.8 V, 2NAND, F/O = 2, standard load) tpd = 136 ps (low-leak : 1.8 V, 2NAND, F/O = 2, standard load)

Leakage Current : 0.023 nW (standard : 1.8 V, 2NAND, F/O = 0, no load)

3.922 nW (ultra high-speed : 1.8 V, 2NAND, F/O = 0, no load) 0.0067 nW (low-leak : 1.8 V, 2NAND, F/O = 0, no load)

Gate power consumption : 40.1 nW/MHz (standard : 1.8 V, 2NAND, F/O = 1, 4Grid)

42.7 nW/MHz (ultra high-speed : 1.8 V, 2NAND, F/O = 1, 4Grid) 38.3 nW/MHz (low-leak : 1.8 V, 2NAND, F/O = 1, 4Grid)

Junction temperature range : -40 to +125 °C

Output buffer cells with noise reduction circuits

Inputs with on-chip input pull-up/pull-down resistors and bidirectional buffer cells.

Buffer cells for crystal oscillation circuits.

Special interfaces : SSTL2, PCI, P-CML, T-LVTTL, USB2.0, IEEE1394, and others

IP macros : CPU (FR-V, ARM9, and others), DSP, PCI, IEEE1394, USB2.0, IrDA, PLL, ADC, DAC,

and others

Compiled cells (RAM/ROM/FIFO/Delay line, and others)

Configurable internal bus circuits

Advanced for hardware/software co-design environment Short-term development using a physical synthesis tool Low-power dissipation using a low power synthesis tool Short-term development using a timing driven layout tool

Hierarchical design environment for supporting large-scale circuits

Supports signal Integrity

Supports memory (RAM, ROM) SCAN

Supports memory (RAM) BIST Supports boundary SCAN Supports path delay test Supports transition delay test

Package lineup : QFP, LQFP, HQFP, FBGA

Packages

The table below lists the available package types.

Туре	Pin Count	Material
QFP	208, 240	Plastics
LQFP	144, 176, 208, 256	Plastics
HQFP	208, 240, 256, 304	Plastics
FBGA	112, 144, 176, 192, 224, 272, 288, 240, 304, 368	Plastics

Note: Contact Fujitsu Microelectronics for the availability.

CS81 Series

Optimum gate count : Maximum of 40,000,000 gates

: 0.18 µm Si-gate CMOS, 4- to 6-layer wiring Technology

Capable of integrating a mixture of high-speed processes and cells on a single chip

Supply voltage : $+1.8 \text{ V} \pm 0.15 \text{V}$ to $+1.1 \text{V} \pm 0.1 \text{V}$ Gate delay time tpd = 11 ps (1.8 V, Inverter, F/O = 1): 5nW/MHz/BC (1.1V, 2NAND, F/O = 1) Gate power consumption

Junction temperature range : -40 to +125 °C High-speed interface macro (up to 3.125 Gbps) Output buffer cells with noise reduction circuits

Inputs with on-chip input pull-up/pull-down resistors (33 k Ω typical) and bidirectional buffer cells.

Buffer cells for crystal oscillation circuits.

Special interfaces: P-CML, LVDS, PCI, AGP, USB, SDRAM-I/F, SSTL, and others IP macros: CPU, DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others

Compiled cells (RAM/ROM/multiplier, and others)

Configurable internal bus circuits

Advanced for hardware/software co-design environment Short-term development using a timing driven layout tool

Supports static timing sign-off

Dramatically reducing the time for generating test vectors for timing verification and the simulation time

Hierarchical design environment for supporting large-scale circuits

Simulation (before layout) considering the input through rate and high resolution RC extraction base delay calculation (after layout), supporting development with minimized timing trouble after trial manufacture.

Supports signal Integrity, EMI noise reduction Supports memory (RAM, ROM) SCAN Supports memory (RAM) BIST

Supports boundary SCAN

Supports At-Speed test on internal circuits

Supports path delay test Supports transition delay test

Package lineup: HQFP, LQFP, FBGA, FC-BGA

Packages

The table below lists the available package types.

Туре	Pin Count	Material
HQFP	208, 240, 256, 304	Plastics
LQFP	144, 176, 208	Plastics
FBGA	112, 133, 176, 192, 224, 240, 272, 288, 304, 368	Plastics
FC-BGA	1089, 1225, 1369, 1681, 1849, 2116	Plastics, Ceramic

Note: Contact Fujitsu Microelectronics for the availability.

Standard Cell

CS66 Series

Features

Optimum gate count : Maximum of 1,700,000 gates

Technology : 0.35 µm Si-gate, 3- to 4-layer metal wiring

: $+3.3 \text{ V} \pm 0.3 \text{ V}$ to $+2.0 \text{ V} \pm 0.1 \text{ V}$ Supply voltage

+5.0 V ± 10% (only for external interface; when internal requirements is 3.3 V)

+3.3 V ± 10% (only for external interface; when internal requirements is 3.3 to 2.0 V)

: t_{pd} = 91 ps (high-speed type, F/O = 2, standard load) Gate delay time

Gate power consumption $0.29 \,\mu\text{W/MHz}$ (F/O = 2, standard load) Junction temperature range $0.40 \,\mu\text{W/MHz}$: -40 to +125°C

High-load driving capability: I_{OL} = 2 mA/4mA/8mA/12mA/24mA mixable.

Output buffer cells with noise reduction circuits

On-chip input pull-up/pull-down resistors (50 k Ω typical)

Buffer cells for crystal oscillation circuits.

Configurable internal bus circuits

Highly integrated RAM/ROM/multipliers mountable; arbitrary words/bits configurable.

Clock skew layout design method (Cadence "CT-Gen") based on the floor plan information minimizes post-layout circuit modification, reducing turnaround time for development.

Simulation (before layout) considering the input through rate and detailed RC delay calculation (after layout),

supporting development with minimized timing trouble after trial manufacture.

Special interface (T-LVTTL and SDRAM-I/F, and others)

Analog PLL

Analog circuits (ADC, DAC, OPAMP and others)

Macros for system ASICs (CPU core, CPU peripheral, operation macro, and others)

Supports DFF scan test with MUX Supports memory (RAM/ROM) scan Supports memory (RAM) BIST Supports boundary SCAN

Standard Cell

Number of gates used in each package
The table below lists the available package types and the reference number of gates used.
CS66 (P-frame)

Package and pin count		0 2000K 4000K 6000K 8000K 10000K 12000K 14000K 1	6000K
LQFP	100 144 176 208	1305K	— 1579K — 1579K — 1579K
QFP	120 144 160 176 208 240 256		107010
HQFP	208 240 256 304		— 1579K — 1579K — 1579K — 1579K
PBGA	256 352		─ 1579K ─ 1579K
FBGA	112 144 168 176 192 224 288	639K 639K 835K 1305K	— 1579K — 1579K — 1579K

CS66 (S-frame)

-											
Package and pin count		0 	100K	200K	300K	400K	500K	600K	700K	800K	900K
LQFP	100 144 208			— 158K — 158K			433K				
QFP	120 144 160 176 208 240	_		— 158K ———2	28K 28K	– 358K		- 545K			
HQFP	208 240 256	_						- 545K - 545K			
PBGA	256 352							- 545K		807	К
FBGA	112 144 168 176 192 224 288			2	228K	(433K 433K			807	к

CE81 Series

Features

High Integration : Maximum of 34,000,000 BCs

Technology : 0.18 μm Si-gate CMOS, 4- to 6*1 -layer wiring

Supply voltage : $+1.8 \text{ V} \pm 0.15 \text{ V}$ to $+1.1 \text{ V} \pm 0.1 \text{ V}$ Gate delay time : $+1.8 \text{ V} \pm 0.15 \text{ V}$ to $+1.1 \text{ V} \pm 0.1 \text{ V}$ tpd = 12 ps (1.8V, Inverter, F/O = 1) Gate power consumption : $+1.8 \text{ V} \pm 0.15 \text{ V}$ to $+1.1 \text{ V} \pm 0.1 \text{ V}$ in the supple of the

Junction temperature range : -40 to +125 °C Output buffer cells with noise reduction circuits

Inputs with on-chip input pull-up/pull-down resistors (33 k Ω typical) and bidirectional buffer cells.

Buffer cells for crystal oscillation circuits.

Special interfaces: P-CML, LVDS, PCI, AGP, USB, SDRAM-I/F, SSTL, and others IP macros: CPU, DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others

Compiled cells (RAM/ROM/multipliers, and others)

Configurable internal bus circuits

Advanced for hardware/software co-design environment Short-term development using a timing driven layout tool

Supports static timing sign-off

Dramatically reducing the time for generating test vectors for timing verification and the simulation time.

Hierarchical design environment for supporting large-scale circuits

Supports optimization environment of power supply wire

Simulation (before layout) considering of the input through rate and high resolution RC extraction base delay calculation (after layout), supporting development with minimized timing trouble after trial manufacture.

Supports Signal Integrity

Supports memory (RAM, ROM) SCAN

Supports memory (RAM) BIST

Supports boundary SCAN

Supports At-Speed test on internal circuits

Supports path delay test Supports transition delay test

Package lineup: HQFP, FBGA, LQFP Note: Some items are in preparation.

Number of gates used in package

The table below lists the available package types and the reference number of gates used.

Package and pin count		0 2000K 4000K 6000K 8000K 10000K 12000K 14000K	16000K
HQFP	208 240 256 304 304		- 15158K
LQFP	144 176 208	722K 	
FBGA	112 176 192 240 288 368	— 514K — 722K — 1098K — 2697K — 2697K — 4712K	

^{*1:} The 6-layer of the CE81 is dedicated for power supply (care required).

CE77 Series

Features

High integration : Maximum of 10,000,000 BCs

Technology : 0.25 µm Si-gate CMOS, 3- to 4-layer wiring

: $+2.5 \text{ V} \pm 0.2 \text{ V}$ to $+1.5 \text{ V} \pm 0.1 \text{ V}$ Supply voltage

Junction temperature range : -40 to +125°C

: $t_{pd} = 33 \text{ ps}$ (2.5 V, Inverter, F/O = 1, No load) Gate delay time : $0.02 \,\mu\text{W/MHz}$ (1.5 V, Inverter, F/O = 1, No load) Gate power consumption

High-load driving capability : $I_{OL} = 2mA/4mA/8mA/12mA$ mixable.

Output buffer cells with noise reduction circuits

Inputs with on-chip input pull-up/pull-down resistors (25 k Ω typical) and bidirectional buffer cells.

Buffer cells for crystal oscillation circuits.

Special interfaces (P-CML, LVDS, T-LVTTL, SSTL, PCI, USB, GTL+, and others) IP macros (CPU, PCI, USB, IrDA, PLL, DAC, ADC, and others)

Compiled cells (RAM/ROM/FIFO/Delay Line, and others)

Configurable internal bus circuits

Advanced for hardware/software co-design environment Short-term development using a timing driven layout tool

Hierarchical design environment for supporting large-scale circuits

Supports static timing sign-off

Dramatically reducing the time for generating test vectors for timing verification and the simulation time.

Simulation (before layout) considering the input through rate and detailed RC delay calculation (after layout),

supporting development with minimized timing trouble after trial manufacture.

Supports memory (RAM, ROM) SCAN

Supports memory (RAM) BIST Supports boundary SCAN Supports path delay test

Package lineup: SQFP, LQFP, HQFP, FBGA, PBGA

Number of gates used in each package
The table below lists the available package types and the reference number of gates used. CE77 (V-Frame)

Package and pin count		0 1000K 2000K 3000K 4000K 5000K 6000K 7000K 8000K 9000K	Material
SQFP	176 208 240	— 274K —— 803K —— 965K	P P P
HQFP	208 240 256 304	1776K 2276K 1776K 7128K	P P P
PBGA	256	—— 618K	Р

P: Plastic

CE77 (T-Frame)

	kage and n count	0 500K 1000K 1500K 2000K 2500K 3000K 3500K 4000K 4500K 5000K	Material
LQFP	144 176 208 256	976 K 744 K 1375 K 1841 K	P P P
HQFP	208 240 256 304	1375 K 1609 K 2109 K	P P P
FBGA	144 176 224 288	461 K 646 K 1375 K 2109 K	P P P
PBGA	256 352 420	1841 K 2678 K 3789 K	P P P

CE71 Series

Features

High integration : Maximum of 8,000,000 BCs

Technology : 0.25 μm Si-gate CMOS, 3- to 4-layer metal wiring

Supply voltage : $+2.5 \text{ V} \pm 0.2 \text{ V}$ to $+1.5 \text{ V} \pm 0.1 \text{ V}$

(5 V TTL interface is available if 5 V tolerant I/O is adopted. Some frames are under

development.)

Gate delay time : $t_{pd} = 29$ ps (2.5 V, Inverter, F/O = 1, No load)

Gate power consumption : $\dot{0}.060 \,\mu\text{W/MHz}$ (F/O = 1, No load)

Junction temperature range : -40 to +125°C

High-load driving capability : $I_{OL} = 2 \text{ mA/4 mA/8 mA/12 mA mixable.}$

Output buffer cells with noise reduction circuits

Inputs with on-chip input pull-up/pull-down resistors (25 k Ω typical) and bidirectional buffer cells.

Buffer cells for crystal oscillation circuits.

Special interfaces (P-CML, LVDS, SDRAM-I/F, SSTL, and others)

IP macros (SPARClite, FR40, F2MC16LX, PCI, IEEE1394, USB, IrDA, PLL, ADC/DAC, and others)

Compiled cells (RAM/ROM/multipliers, and others)

Configurable internal bus circuits

Advanced for hardware/software co-design environment

Linking floor plan tools and logic synthesis tools allows automatic optimization of the circuits using the floor plan information. The Clock Driven Design Method (CDDM) clock tree synthesis tools using the floor plan information are also available. Using the floor plan information in the pre-layout stage would eliminate the problems of setup after layout or timing problems for hold, significantly reducing the time to market.

Supports the static timing sign off using the Synopsys CAD tool Prime Time. This contributes to the considerable reduction of time required for test vector creation for timing verification and the simulation time.

Simulation (before layout) considering the input through rate and detailed RC delay calculation (after layout),

supporting development with minimized timing trouble after trial manufacture.

Supports memory (RAM, ROM) SCAN

Supports memory (RAM) BIST

Supports boundary SCAN

Package lineup: SQFP, LQFP, HQFP, PBGA, FBGA

Number of gates used in each package

The table below lists the available package types and the reference number of gates used. CE71 (J-Frame)

	ge and count	0 1000K 2000K 3000K 4000K 5000K	Material
SQFP	176 208 240	—— 203K ———— 592K ———— 714K	P P P
HQFP	208 240 256 304	1313K 1681K 1313K 5345K	P P P
PBGA	256	——— 457K	Р

CE71 (T-Frame)

	ge and count	0 1000K 2000K 3000K 4000K 5000K	Material
LQFP	144 176 208 256	—— 341K ——— 477K ———— 1014K ———— 1358K	P P P
HQFP	208 240 256 304		P P P
FBGA	144 176 224 288	—— 341K ——— 477K ———————————————————————————————————	P P P
PBGA	256 352 420		P P P

CE66 Series

Features

High integration : Maximum of 1,138,000 BCs

Technology : 0.35 μm Si-gate, 3- to 4-layer metal wiring

Supply voltage : $+3.3 \text{ V} \pm 0.3 \text{ V}$ to $+2.0 \text{ V} \pm 0.1 \text{ V}$

 $+5.0 \text{ V} \pm 10\%$ (only for external interface; when internal requirements is 3.3 V)

 $+3.3~V \pm 10\%$ (only for external interface; when internal requirements is 3.3 to 2.0 V)

Gate delay time : $t_{pd} = 98$ ps (high-speed type, F/O = 2, standard load)

Gate power consumption : $0.29 \mu W/MHz$ (F/O = 2, standard load)

Junction temperature range : - 40 to 125°C

High-load driving capability: I_{OL} = 2 mA/4mA/8mA/12mA/24mA mixable.

Output buffer cells with noise reduction circuits

On-chip input pull-up/pull-down resistors (50 k Ω typical)

Buffer cells dedicated to crystal oscillator

Configurable internal bus circuits

Highly integrated RAM/ROM/multipliers mountable; arbitrary words/bits configurable.

Clock skew layout design method (CDDM) based on the floor plan information minimizes post-layout circuit modification, reducing turnaround time for development.

Simulation (before layout) considering the input through rate and detailed RC delay calculation (after layout),

supporting development with minimized timing trouble after trial manufacture.

Special interfaces (T-LVTTL and SDRAM-I/F, and others)

Analog PLL

Analog circuits (ADC, DAC, OPAMP and others)

Macros for system ASICs (CPU core, CPU peripheral, operational macros, and others)

Supports DFF scan test with MUX Supports memory (RAM/ROM) SCAN Supports memory (RAM) BIST

Supports memory (RAM) B Supports boundary SCAN

Number of gates used in each package
The table below lists the available package types and the reference number of gates used. CE66 (P-frame)

Package	and pin unt	0 100K 200K 300K 400K 500K 600K 700K 800K 900K 1000K 1100	
LQFP	100 144 176 208	939K	— 1138K — 1138K — 1138K
QFP	120 144 160 176 208 240 256		- 1138K - 1138K - 1138K - 1138K
HQFP	208 240 256 304		- 1138K - 1138K
PBGA	256 352		
FBGA	112 144 168 176 192 224 288	459K 459K 601K 939K	

CE66 (S-frame)

Package and pin count		0 50K 100K 150K 200K 250K 300K 350K 40	00K 450K 500K 550K 600K
LQFP	100 144 208	112K 112K 311K	
QFP	120 144 160 176 208 240		390K
HQFP	208 240 256		390K 390K
PBGA	256 352		390K 579K
FBGA	112 144 168 176 192 224 288		579K

CE61 Series

Features

High Integration : Maximum of 2,000,000 BCs

Technology : 0. 35 μm Si-gate 3-layer metal wiring/4-layer metal wiring

(There are restrictions applicable frames)

Basic circuit (basic cell) : 2-input NAND/2-input NOR gates Supply voltage : $+3.3 \text{ V} \pm 0.3 \text{ V}$ to $+2.0 \text{ V} \pm 0.1 \text{ V}$

High voltage tolerant transistor for I/O; interface provided for 5 V devices

(Also requiring a 5 V power supply for interface with 5 V devices)

Gate delay time : High-speed type, $t_{pd} = 85 \text{ ps}$ (2-input NAND, F/O = 2, standard load)

Junction temperature range : 0 to +100°C

High-load driving capability : I_{OL} = 2 mA/4 mA/8 mA/12 mA/24 mA mixable. Power consumption : Reduced to 50% to 20% (over the CE51 Series)

Output buffer cells with noise reduction circuits On-chip input pull-up/pull-down resistors (Typ. 50kΩ)

Buffer cells for crystal oscillation circuits.

Configurable internal bus circuits

Super high-integration RAM and ROM available. Compilable bit/word configuration

Clock skew reduction layout design technique (CDDM) employed to minimize circuit modification after layout, reducing

Simulation (before layout) considering the input through rate and detailed RC delay calculation (after layout),

supports development with minimized timing trouble after trial manufacture.

Supports high speed interfaces [P-CML (200 MHz transmission), LVDS (250 MHz transmission), and SDRAM I/F, PCI,5

V tolerant, USB, IEEE 1284]

PLL circuits

Analog circuits (ADC, DAC)

Macros for system ASICs (CPU core and CPU peripheral and operational macros, and others)

Supports tests (for function/DC) using DFF scan with MUX

Supports the test for RAM BIST, RAM SCAN and ROM SCAN

Supports the Boundary SCAN

Now under preparation on for a narrow-pitch pad technology and high-pin count BGA packages to be added to the current lineup

Variety of package options to optimize any gate size

Number of gates used in each package)
The table below lists the available package types and the reference number of gates used." CE61 (F10 to F80)

Package and pin count 0 100K 200K 300K 400K 500K 600K 700K 800K 900K 1000K1100K1200K1300K				
QFP	64 80 100 120 144 160 176 176 208 208 240 240 256 256 304		P P P P P P C P C P C P C C P C	
LQFP	64 80 100	86K 86K 86K	P P P	
HQFP	208 240 256 304	981K1317K	P P P	
BGA	256 352 420	593K 981K	P P P	
PGA	256 299 361 401		C C C	

P: Plastic C: Ceramic

CE61 (E7 to E71)

Packag pin co		0 100K 200K 300K 400K 500K 600K 700K 800K 900K 1000K 1100K	Material
QFP	120 144 160 176 208 240 256		P P P P P
LQFP	64 80 100	78K 128K 128K	P P P
HQFP	208 240 256 304		P P P
BGA	256 352 420 576 672	391K 391K 509K 747K	P P P P

CG61 Series (Analog PLL embedment is possible in some frames)

Features

High Integration : 1,560,000 BCs

Technology : 0. 35 µm Si-gate CMOS, 3-layer metal wiring

Basic circuit (basic cell) : 2-input NAND/2-input NOR gates Supply voltage : $+3.3 \text{ V} \pm 0.3 \text{ V}$ to $+2.0 \text{ V} \pm 0.1 \text{ V}$

(5 V TTL interface is possible when 5 V tolerant I/Os are used.)

: t_{pd} = 85 ps (3.3 V, 2-input NAND, F/O = 2, standard load) Gate delay time Gate power dissipation : $\dot{0}$.24 μ W/MHz (2.0 V, 2-input NAND, F/O = 2, standard load)

Junction temperature range : 0 to +100 °C

High-load driving capability : $I_{OL} = 2 \text{ mA/4 mA/8 mA/12 mA/24 mA mixable}$

Output buffer cells with noise reduction circuits

On-chip input pull-up/pull-down resistors (Typ. 50 k Ω <at 3.3 V>)

Buffer cells for crystal oscillation circuits

Configurable internal bus circuits

Compiled RAM can be embedded. Compilable bit/word configuration

An analog PLL can be embedded in CG61P only.

Clock skew reduction layout design technique (CDDM) employed to minimize circuit modification after layout, reducing TAT Simulation (before layout) considering the input through rate and detailed RC delay calculation (after layout),

supports development with minimized timing trouble after trial manufacture.

Supports high speed interfaces (T-LVTTL, P-CML, LVDS, SDRAM I/F)

Supports tests using DFF scan with MUX

Supports the test for RAM BIST and RAM SCAN

Number of gates used in each package
The table below lists the available package types and the reference number of gates used.

CG 61 (The frame which cannot use Analog PLL)

Package and pin count		0 100K 200K 300K 400K 500K 600K 700K 800K 900K	Material
LQFP	120 144	222K 222K	P P
QFP	208 240 256		P P P
HQFP	208 240 256 304		P P P

P: plastic

CG 61P (The frame which can use Analog PLL)

Package and pin count		0 20K 40K 60K 80K 100K 120K 140K 160K 180K 200K	Material
	48	16K	Р
	64	88K	Р
	80	188K	Р
	100	188K	Р
LQFF	120	188K	Р
	144		Р
	176		Р
	208	188K	P
	200	1001	'
OFD	240	188K	Р
QFP	256	188K	Р

P: plastic

CG47 Series

Features

High integration : Maximum 55,000 BCs (on chip)

Technology : 0.65 μm Si-gate CMOS, 2-layer metal wiring Gate delay time : 300ps (power type 2-input NAND, standard load)

Supply voltage : $+5 \text{ V} \pm 5\%$, $+3.3 \text{ V} \pm 0.3 \text{ V}$

[Dual power supply] Internal domain: $+3.3 \text{ V} \pm 0.3 \text{ V}$, $+5 \text{ V} \pm 5\%$ (cannot be mixed)

 $I/O: +3.3 V \pm 0.3 V, +5 V \pm 5\%$ (can be mixed)

Interface enabled between dual power sources

Low power consumption enabled by operating internal supply voltage at 3.3V.

Delay time estimation by detailed time equations

Detailed time equations can be used for the estimation of delay time closer to that of actual devices.

Buffer cells for crystal oscillations circuits

Supports separate low frequency (32 kHz), and high frequency (1 to 40MHz) buffers, and oscillator stop function.

Supports output open drain cell and input fail safe cells

Compiled cells include single port RAM, dual port RAM, and FIFO memory.

Note: The type of the RAM that can be used is specified depending on the internal power supply when the RAM is a single-port RAM.

HISCAN (scan circuit automatic generation function)

HISCAN is supported with single power supply, but dual power supply specifications and HISCAN are mutually exclusive.

Simple interface

CAD-to-CAD interface uses special language for logic data (FLDL) and test data (FTDL).

Integrated development tools

Number of gates used in each package

The table below lists the available package types and the reference number of gates used.

Package and pin count		0 5K 10K 15K 20K 25K 30K 35K 40K 45K 50K
LQFP	48 64 80 100 120 144 176 208	
QFP	240	33К

CG46 Series

Features

High integration : Maximum 198,084 BCs (on chip)

: 0.65 μm Si-gate CMOS, 2-layer metal wiring : 2-input NAND/2-input NOR gates Technology

Basic circuit (basic cell)

Input level : TTL/CMOS level mixable

Supply voltage : +5 V ± 5%

 $+3.3 \text{ V} \pm 0.3 \text{ V}$ (optional)

Gate delay time tpd = 360 ps (2-input NAND, standard load) : Standard gate Power gate tpd = 300 ps (2-input NAND, standard load)

Operating temperature : 0 to +70°C

High-load driving capability: I_{OL} = 3.2 mA/8 mA/12 mA/24 mA mixable

Output buffer cells with noise reduction circuits

On-chip input pull-up/pull-down resistors (Typ. 50 k Ω)

Buffer cells for crystal oscillations circuits

Configurable internal bus circuits

RAM and FIFO memory allowing arbitrary bit/word configuration

Clock skew reduction layout design technique (CDDM) employed to minimize circuit modification after layout, reducing the period of time for development

Delailed RC delay calculation minimized timing trouble after trial manufacture.

Supports ATG (Automatic Test Generation) based on scan design

Supports HISCAN (automatic scan generation)

Simplified interface: CAD-to-CAD interface uses special language for logic data (FLDL) and test data (FTDL).

Integrated development tools

Number of gates used in each package

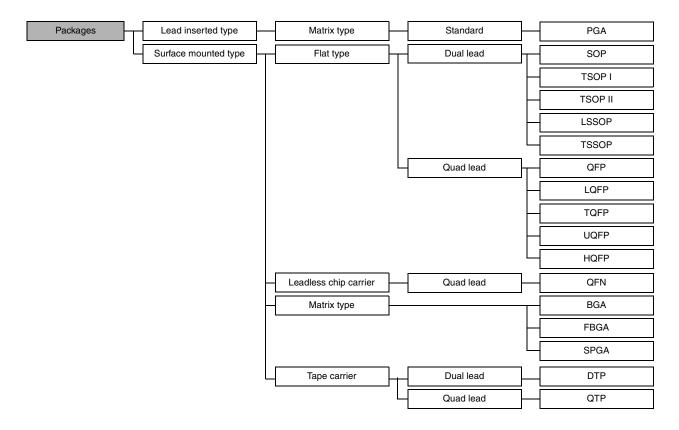
The table below lists the available package types and the reference number of gates used.

Package and pin count		Number of gates used (BC)				
		0 10K 20K 30K 40K 50K 60K 70K 80K 90K 100K				
LQFP	48 64 80 100	10K 42K 65K				
LQII	120 144 176 208	50K 50K 50K				
QFP	208 240	50K 50K				

Package Line-up

■ Package Line-up

The packages are classified as follows, according to form, material, and the mounting methods for which they are suited.



Package Line-up

Name of package	Description	Lead pitch (mm)	
PGA	Pin Grid Array Package	1.27/2.54	
SOP	Small Outline Package (straight lead) Small Outline L-Leaded Package	1.27	
SOL*2	Small Outline L-Leaded Package (JEDEC*1)	1.27	
SSOP	Shrink Small Outline L-Leaded Package	0.65/0.80/1.00	
TSOP (I)	Thin Small Outline L-Leaded Package (I)	0.50/0.55/0.60	
TSOP (II)	Thin Small Outline L-Leaded Package (II)	0.50/0.80/1.00/1.27	
SON	Small Outline Non-Leaded Package	0.50/1.00	
QFP	Quad Flat Package (straight lead) Quad Flat L-Leaded Package	0.40/0.50/0.65/0.80/1.00	
LQFP*2	Low-Profile Quad Flat L-Leaded Package	0.40/0.50/0.65/0.80	
TQFP	Thin Quad Flat L-Leaded Package	0.40/0.50	
HQFP	QFP with Heat Sink	0.40/0.50/0.65	
LCC ^{*2}	Leadless Chip Carrier	4 040/4 07	
QFN	Quad Flat Non-Leaded Package	1.016/1.27	
BGA	Ball Grid Array	1.27/1.0	
FBGA	Fine pitch Ball Grid Array	0.8/0.75/0.65/0.5	
DTP	Dual Tape Carrier Package	_	
QTP	Quad Tape Carrier Package	_	

^{*1:} Joint Electron Device Engineering Council

^{*2:} Package name used by Fujitsu Microelectronics

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FAR-F4SE-44M000-H0AA	18	_
FAR-F4SE-44M000-H0AG	18	_
FAR-F4SE-44M000-H0AH	18	_
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FAR-F6KB-1G8425-B4GA	12	-
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FAR-F6KB-1G9500-B4GJ	12	-
FAR-F6KB-1G9600-B4GB	12	-
FAR-F6KB-1G9600-B4GP	12	-
FAR-F6KB-2G1400-B4GC	12	-
FAR-F6KB-2G4418-B4GL	12	-
FAR-G5KG-942M50-Y4SD	12	-
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FAR-G5KL-911M50-D4XC	12	-
FAR-G6KE-1G9600-Y4LY	12	-
FAR-G6KG-1G8425-Y4SA	12	-
FAR-G6KG-1G9500-Y4PG	12	-
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FAR-G6KG-1G9600-Y4SC	12	-
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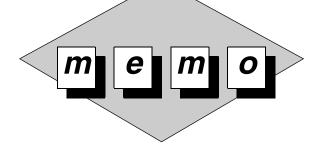
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FUJITSU MICROELECTRONICS LIMITED

Shinjuku Dai-Ichi Seimei Bldg., 7-1, Nishishinjuku 2-chome, Shinjuku-ku, Tokyo 163-0722, Japan Tel: +81-3-5322-3329 http://jp.fujitsu.com/fml/en/

For further information please contact:

North and South America

FUJITSU MICROELECTRONICS AMERICA, INC. 1250 E. Arques Avenue, M/S 333
Sunnyvale, CA 94085-5401, U.S.A.
Tel: +1-408-737-5600 Fax: +1-408-737-5999
http://www.fma.fujitsu.com/

Europe

FUJITSU MICROELECTRONICS EUROPE GmbH Pittlerstrasse 47, 63225 Langen, Germany Tel: +49-6103-690-0 Fax: +49-6103-690-122 http://emea.fujitsu.com/microelectronics/

Korea

FUJITSU MICROELECTRONICS KOREA LTD. 206 Kosmo Tower Building, 1002 Daechi-Dong, Gangnam-Gu, Seoul 135-280, Republic of Korea Tel: +82-2-3484-7110 Fax: +82-2-3484-7111 http://kr.fujitsu.com/fmk/

Asia Pacific

FUJITSU MICROELECTRONICS ASIA PTE. LTD. 151 Lorong Chuan, #05-08 New Tech Park 556741 Singapore Tel: +65-6281-0770 Fax: +65-6281-0220 http://www.fmal.fujitsu.com/

FUJITSU MICROELECTRONICS SHANGHAI CO., LTD. Rm.3102, Bund Center, No.222 Yan An Road(E), Shanghai 200002, China Tel: +86-21-6146-3688 Fax: +86-21-6335-1605 http://cn.fujitsu.com/fmc/

FUJITSU MICROELECTRONICS PACIFIC ASIA LTD. 10/F., World Commerce Centre, 11 Canton Road, Tsimshatsui, Kowloon, Hong Kong

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